

**K9F1208U0C**  
**K9F1208R0C K9F1208B0C**

**FLASH MEMORY**

# K9F1208X0C

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Document Title

64M x 8 Bits NAND Flash Memory

勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

Revision History

| <u>Revision No.</u> | <u>History</u>   | <u>Draft Date</u> | <u>Remark</u> |
|---------------------|--|-------------------|---------------|
| 0.0                 | Initial issue.   | Nov. 10th 2005    | Advance       |
| 0.1                 | 2.7V part is added   | July 13th 2006    | Advance       |
| 0.2                 | Address of Read 2 is changed (A <sub>4</sub> -A <sub>7</sub> : Don't care -> Fixed "Low" ) | Aug. 1st 2006     | Advance       |
| 0.3                 | 1. Add tRPS/tRCS/tREAS parameter for status read<br>2. Add nWP timing guide                | Oct. 12th 2006    | Advance       |
| 0.4                 | 1. Change from tRPS/tRCS/tREAS to tRPB/tRCB/tREAB parameter for 1.8V device busy state     | Nov. 14th 2006    | Advance       |
| 0.5                 | 1. Sequential Row Read is added  | Nov. 15th 2006    | Preliminary   |
| 1.0                 | 1. tCRY is changed (50ns+tR(R/B) --> 5us)  | Dec. 28th 2006    | Final         |

Note : For more detailed features and specifications including FAQ, please refer to Samsung's Flash web site.  
<http://www.samsung.com/Products/Semiconductor/>

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## FLASH MEMORY

### 64M x 8 Bits NAND Flash Memory

#### PRODUCT LIST

| Part Number  | Vcc Range     | Organization | PKG Type |
|--------------|---------------|--------------|----------|
| K9F1208R0C-J | 1.65V ~ 1.95V | x8           | FBGA     |
| K9F1208B0C-P | 2.5V ~ 2.9V   |              | TSOP1    |
| K9F1208U0C-P | 2.7V ~ 3.6V   |              | TSOP1    |
| K9F1208U0C-J |               |              | FBGA     |

#### FEATURES

- Voltage Supply
  - 1.8V Device(K9F1208R0C) : 1.65V ~ 1.95V
  - 2.7V Device(K9F1208B0C) : 2.5V ~ 2.9V
  - 3.3V Device(K9F1208U0C) : 2.7V ~ 3.6V
- Organization
  - Memory Cell Array : (64M + 2M) x 8bits
  - Data Register : (512 + 16) x 8bits
- Automatic Program and Erase
  - Page Program : (512 + 16) x 8bits
  - Block Erase : (16K + 512)Bytes
- Page Read Operation
  - Page Size : (512 + 16)Bytes
  - Random Access : 15μs(Max.)
  - Serial Page Access : 42ns(Min.)
- Fast Write Cycle Time
  - Program time : 200μs(Typ.)
  - Block Erase Time : 2ms(Typ.)
- Command/Address/Data Multiplexed I/O Port
- Hardware Data Protection
  - Program/Erase Lockout During Power Transitions
- Reliable CMOS Floating-Gate Technology
  - Endurance : 100K Program/Erase Cycles (with 1bit/512Byte ECC)
  - Data Retention : 10 Years
- Command Register Operation
- Unique ID for Copyright Protection
- Package
  - K9F1208U0C-PCB0/PIB0 : Pb-Free Package 48 - Pin TSOP I (12 x 20 / 0.5 mm pitch)
  - K9F1208X0C-JCB0/JIB0 : Pb-Free Package 63-Ball FBGA(8.5 x 13 x 1.2mmt)
  - K9F1208B0C-PCB0/PIB0 : Pb-Free Package 48 - Pin TSOP I (12 x 20 / 0.5 mm pitch)

#### GENERAL DESCRIPTION

Offered in 64Mx8bits, the K9F1208X0C is 512Mbit with spare 16Mbit capacity. The device is offered in 1.8V, 2.7V and 3.3V Vcc. Its NAND cell provides the most cost-effective solution for the solid state mass storage market. A program operation can be performed in typical 200μs on the 528-bytes and an erase operation can be performed in typical 2ms on a 16K-bytes block. Data in the page can be read out at 42ns cycle time per byte. The I/O pins serve as the ports for address and data input/output as well as command input. The on-chip write control automates all program and erase functions including pulse repetition, where required, and internal verification and margining of data. Even the write-intensive systems can take advantage of the K9F1208X0C's extended reliability of 100K program/erase cycles by providing ECC(Error Correcting Code) with real time mapping-out algorithm. The K9F1208X0C is an optimum solution for large nonvolatile storage applications such as solid state file storage and other portable applications requiring non-volatility.



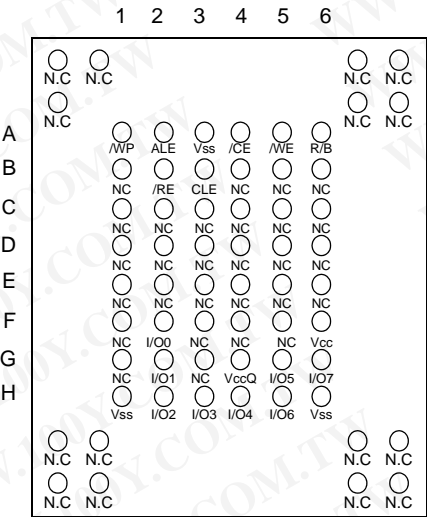


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PIN CONFIGURATION (FBGA)

K9F1208X0C-JCB0/JIB0



Top View

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**PIN DESCRIPTION**

| Pin Name                            | Pin Function  |
|-------------------------------------|---|
| I/O <sub>0</sub> ~ I/O <sub>7</sub> | <b>DATA INPUTS/OUTPUTS</b><br>The I/O pins are used to input command, address and data, and to output data during read operations. The I/O pins float to high-z when the chip is deselected or when the outputs are disabled.   |
| CLE                                 | <b>COMMAND LATCH ENABLE</b><br>The CLE input controls the activating path for commands sent to the command register. When active high, commands are latched into the command register through the I/O ports on the rising edge of the $\overline{WE}$ signal.   |
| ALE                                 | <b>ADDRESS LATCH ENABLE</b><br>The ALE input controls the activating path for address to the internal address registers. Addresses are latched on the rising edge of $\overline{WE}$ with ALE high.   |
| $\overline{CE}$                     | <b>CHIP ENABLE</b><br>The $\overline{CE}$ input is the device selection control. When the device is in the Busy state, $\overline{CE}$ high is ignored, and the device does not return to standby mode in program or erase operation. Regarding $\overline{CE}$ control during read operation, refer to 'Page read' section of Device operation.                  |
| $\overline{RE}$                     | <b>READ ENABLE</b><br>The $\overline{RE}$ input is the serial data-out control, and when active drives the data onto the I/O bus. Data is valid tREA after the falling edge of $\overline{RE}$ which also increments the internal column address counter by one.  |
| $\overline{WE}$                     | <b>WRITE ENABLE</b><br>The $\overline{WE}$ input controls writes to the I/O port. Commands, address and data are latched on the rising edge of the $\overline{WE}$ pulse.   |
| $\overline{WP}$                     | <b>WRITE PROTECT</b><br>The $\overline{WP}$ pin provides inadvertent write/erase protection during power transitions. The internal high voltage generator is reset when the $\overline{WP}$ pin is active low.  |
| R/ $\overline{B}$                   | <b>READY/BUSY OUTPUT</b><br>The R/ $\overline{B}$ output indicates the status of the device operation. When low, it indicates that a program, erase or random read operation is in process and returns to high state upon completion. It is an open drain output and does not float to high-z condition when the chip is deselected or when outputs are disabled. |
| Vcc                                 | <b>POWER</b><br>Vcc is the power supply for device.   |
| Vss                                 | <b>GROUND</b>   |
| N.C                                 | <b>NO CONNECTION</b><br>Lead is not internally connected.   |
| DNU                                 | <b>DO NOT USE</b><br>Leave it disconnected.   |

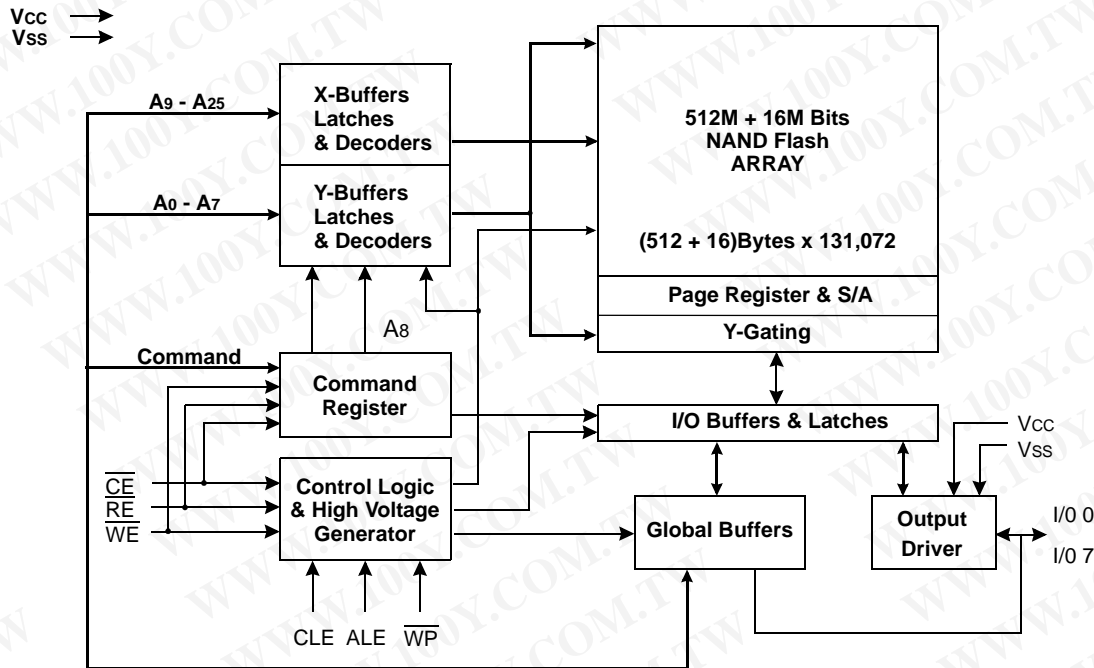
**NOTE :** Connect all Vcc and Vss pins of each device to common power supply outputs.

Do not leave Vcc or Vss disconnected.

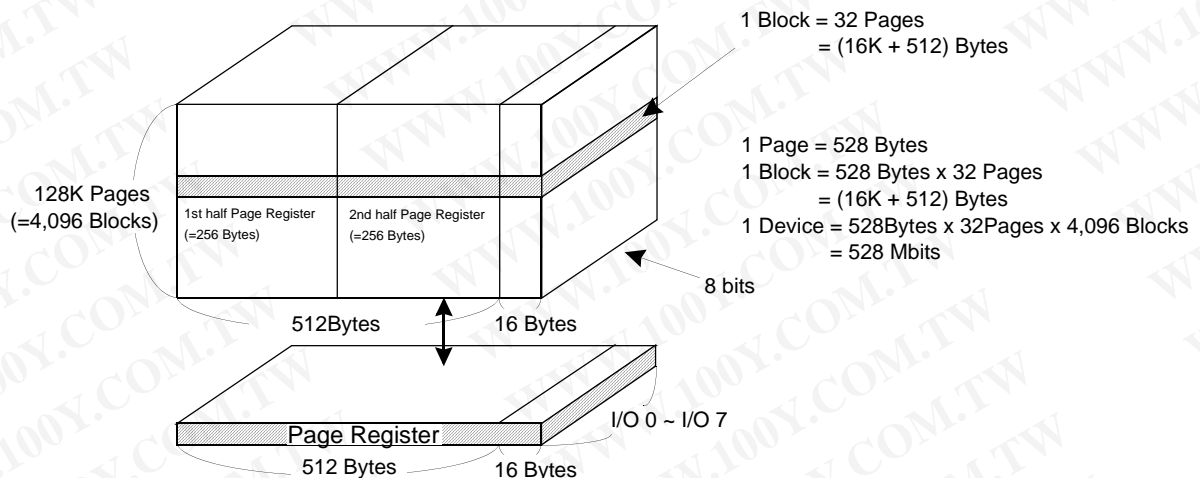
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**Figure 1. K9F1208X0C FUNCTIONAL BLOCK DIAGRAM**



**Figure 2. K9F1208X0C ARRAY ORGANIZATION**



|           | I/O 0 | I/O 1 | I/O 2 | I/O 3 | I/O 4 | I/O 5 | I/O 6 | I/O 7 |
|-----------|-------|-------|-------|-------|-------|-------|-------|-------|
| 1st Cycle | A0    | A1    | A2    | A3    | A4    | A5    | A6    | A7    |
| 2nd Cycle | A9    | A10   | A11   | A12   | A13   | A14   | A15   | A16   |
| 3rd Cycle | A17   | A18   | A19   | A20   | A21   | A22   | A23   | A24   |
| 4th Cycle | A25   | *L    | *L    | *L    | *L    | *L    | *L    | *L    |

**Column Address**  
**Row Address**  
**(Page Address)**

**NOTE :** Column Address : Starting Address of the Register.

00h Command(Read) : Defines the starting address of the 1st half of the register.

01h Command(Read) : Defines the starting address of the 2nd half of the register.

\* A8 is set to "Low" or "High" by the 00h or 01h Command.

\* L must be set to "Low".

\* The device ignores any additional input of address cycles than required.



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### Product Introduction

The K9F1208X0C is a 528Mbits(553,648,218 bits) memory organized as 131,072 rows(pages) by 528 columns. Spare sixteen columns are located from column address of 512 to 527. A 528-bytes data register is connected to memory cell arrays accommodating data transfer between the I/O buffers and memory during page read and page program operations. The memory array is made up of 16 cells that are serially connected to form a NAND structure. Each of the 16 cells resides in a different page. A block consists of the 32 pages formed two NAND structures. A NAND structure consists of 16 cells. Total 135,168 NAND structures reside in a block. The program and read operations are executed on a page basis, while the erase operation is executed on a block basis. The memory array consists of 4,096 separately erasable 16K-bytes blocks. It indicates that the bit by bit erase operation is prohibited on the K9F1208X0C.

The K9F1208X0C has addresses multiplexed into 8 I/O's. This scheme dramatically reduces pin counts and allows systems upgrades to future densities by maintaining consistency in system board design. Command, address and data are all written through I/O's by bringing WE to low while CE is low. Data is latched on the rising edge of WE. Command Latch Enable(CLE) and Address Latch Enable(ALE) are used to multiplex command and address respectively, via the I/O pins. The 64M byte physical space requires 26 addresses, thereby requiring four cycles for byte-level addressing : 1 cycle of column address, 3 cycles of row address, in that order. Page Read and Page Program need the same four address cycles following the required command input. In Block Erase operation, however, only the 3 cycles of row address are used. Device operations are selected by writing specific commands into the command register. Table 1 defines the specific commands of the K9F1208X0C.

**Table 1. Command Sets**

| Function               | 1'st Cycle             | 2'nd Cycle | Acceptable Command during Busy |
|------------------------|------------------------|------------|--------------------------------|
| Read 1                 | 00h/01h <sup>(1)</sup> | -          |                                |
| Read 2                 | 50h                    | -          |                                |
| Read ID                | 90h                    | -          |                                |
| Reset                  | FFh                    | -          | O                              |
| Page Program           | 80h                    | 10h        |                                |
| Block Erase            | 60h                    | D0h        |                                |
| Block Protect 1        | 41h                    | -          |                                |
| Block Protect 2        | 42h                    | -          |                                |
| Block Protect 3        | 43h                    | -          |                                |
| Read Status            | 70h                    | -          | O                              |
| Read Protection Status | 7Ah                    | -          |                                |

**NOTE :** 1. The 00h/01h command defines starting address of the 1st/2nd half of registers.

After data access on the 2nd half of register by the 01h command, the status pointer is automatically moved to the 1st half register(00h) on the next cycle.

**Caution :** Any undefined command inputs are prohibited except for above command set of Table 1.

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### ABSOLUTE MAXIMUM RATINGS

| Parameter                          |                 | Symbol            | Rating                                  |  | Unit |
|------------------------------------|-----------------|-------------------|---|--|------|
|                                    |                 |                   | 1.8V Device                             | 2.7V/3.3V Device                       |      |
| Voltage on any pin relative to VSS |                 | V <sub>CC</sub>   | -0.6 to + 2.45                          | -0.6 to + 4.6                          | V    |
|                                    |                 | V <sub>IN</sub>   | -0.6 to + 2.45                          | -0.6 to + 4.6                          |      |
|                                    |                 | V <sub>I/O</sub>  | -0.6 to V <sub>CC</sub> + 0.3 (< 2.45V) | -0.6 to V <sub>CC</sub> + 0.3 (< 4.6V) |      |
| Temperature Under Bias             | K9F1208X0C-XCB0 | T <sub>BIAS</sub> | -10 to +125                             |  | °C   |
|                                    | K9F1208X0C-XIB0 |                   | -40 to +125                             |  |      |
| Storage Temperature                | K9F1208X0C-XCB0 | T <sub>STG</sub>  | -65 to +150                             |  | °C   |
|                                    | K9F1208X0C-XIB0 |                   |   |  |      |
| Short Circuit Current              |                 | I <sub>OS</sub>   | 5                                       |  | mA   |

#### NOTE :

1. Minimum DC voltage is -0.6V on input/output pins. During transitions, this level may undershoot to -2.0V for periods <30ns.  
Maximum DC voltage on input/output pins is VCC+0.3V which, during transitions, may overshoot to VCC+2.0V for periods <20ns.
2. Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### RECOMMENDED OPERATING CONDITIONS

(Voltage reference to GND at the condition of K9F1208X0C-XCB0 : TA=0 to 70°C or K9F1208X0C-XIB0 : TA=-40 to 85°C)

| Parameter      | Symbol | 1.8V(K9F1208R0C) |      |      | 2.7V(K9F1208B0C) |      |     | 3.3V(K9F1208U0C) |      |     | Unit |
|----------------|--------|------------------|------|------|------------------|------|-----|------------------|------|-----|------|
|                |        | Min              | Typ. | Max  | Min              | Typ. | Max | Min              | Typ. | Max |      |
| Supply Voltage | VCC    | 1.65             | 1.8  | 1.95 | 2.5              | 2.7  | 2.9 | 2.7              | 3.3  | 3.6 | V    |
|                | VSS    | 0                | 0    | 0    | 0                | 0    | 0   | 0                | 0    | 0   | V    |

### DC AND OPERATING CHARACTERISTICS (Recommended operating conditions otherwise noted.)

| Parameter                     |                 | Symbol                | Test Conditions   | K9F1208X0C           |     |                      |                      |     |                      |      |     |                      | Unit |
|-------------------------------|-----------------|-----------------------|---|----------------------|-----|----------------------|----------------------|-----|----------------------|------|-----|----------------------|------|
|                               |                 |                       |   | 1.8V                 |     |                      | 2.7V                 |     |                      | 3.3V |     |                      |      |
|                               |                 |                       |   | Min                  | Typ | Max                  | Min                  | Typ | Max                  | Min  | Typ | Max                  |      |
| Operating Current             | Sequential Read | ICC1                  | tRC=42ns, CE=V <sub>IL</sub> , I <sub>OUT</sub> =0mA  | -                    | 8   | 20                   | -                    | 10  | 20                   | -    | 10  | 20                   | mA   |
|                               | Program         | ICC2                  | -   | -                    | 8   | 20                   | -                    | 10  | 20                   | -    | 10  | 20                   |      |
|                               | Erase           | ICC3                  | -   | -                    | 8   | 20                   | -                    | 10  | 20                   | -    | 10  | 20                   |      |
| Stand-by Current(TTL)         |                 | ISB1                  | CE=V <sub>IH</sub> , WP=0V/V <sub>CC</sub>  | -                    | -   | 1                    | -                    | -   | 1                    | -    | -   | 1                    | µA   |
| Stand-by Current(CMOS)        |                 | ISB2                  | CE=V <sub>CC</sub> -0.2, WP=0V/V <sub>CC</sub>  | -                    | 10  | 50                   | -                    | 10  | 50                   | -    | 10  | 50                   |      |
| Input Leakage Current         |                 | I <sub>LI</sub>       | V <sub>IN</sub> =0 to V <sub>cc</sub> (max)   | -                    | -   | ±10                  | -                    | -   | ±10                  | -    | -   | ±10                  |      |
| Output Leakage Current        |                 | I <sub>LO</sub>       | V <sub>OUT</sub> =0 to V <sub>cc</sub> (max)  | -                    | -   | ±10                  | -                    | -   | ±10                  | -    | -   | ±10                  | V    |
| Input High Voltage            |                 | V <sub>IH</sub>       |   | V <sub>CC</sub> -0.4 | -   | V <sub>CC</sub> +0.3 | V <sub>CC</sub> -0.4 | -   | V <sub>CC</sub> +0.3 | 2.0  | -   | V <sub>CC</sub> +0.3 |      |
| Input Low Voltage, All inputs |                 | V <sub>IL</sub>       | -   | -0.3                 | -   | 0.4                  | -0.3                 | -   | 0.5                  | -0.3 | -   | 0.8                  |      |
| Output High Voltage Level     |                 | V <sub>OH</sub>       | K9F1208R0C: I <sub>OH</sub> =-100µA<br>K9F1208B0C: I <sub>OH</sub> =-100µA<br>K9F1208U0C: I <sub>OH</sub> =-400µA | V <sub>CC</sub> -0.1 | -   | -                    | V <sub>CC</sub> -0.4 | -   | -                    | 2.4  | -   | -                    |      |
| Output Low Voltage Level      |                 | V <sub>OL</sub>       | K9F1208R0C: I <sub>OL</sub> =100µA<br>K9F1208B0C: I <sub>OL</sub> =100µA<br>K9F1208U0C: I <sub>OL</sub> =2.1mA    | -                    | -   | 0.1                  | -                    | -   | 0.4                  | -    | -   | 0.4                  |      |
| Output Low Current(R/B)       |                 | I <sub>OL</sub> (R/B) | V <sub>OL</sub> =0.4V   | 3                    | 4   | -                    | 3                    | 4   | -                    | 8    | 10  | -                    | mA   |

#### Notes :

1. Typical values are measured at VCC=3.3V, TA=25°C. And not 100% tested.

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### VALID BLOCK

| Parameter          | Symbol | Min   | Typ. | Max   | Unit   |
|--------------------|--------|-------|------|-------|--------|
| Valid Block Number | NvB    | 4,026 | -    | 4,096 | Blocks |

#### NOTE :

1. The K9F1208X0C may include invalid blocks when first shipped. Additional invalid blocks may develop while being used. The number of valid blocks is presented with both cases of invalid blocks considered. Invalid blocks are defined as blocks that contain one or more bad bits. Do not erase or program factory-marked bad blocks. Refer to the attached technical notes for a appropriate management of invalid blocks.
2. The 1st block, which is placed on 00h block address, is guaranteed to be a valid block up to 1K program/erase cycles with 1bit/512Byte ECC.
3. Minimum 1,004 valid blocks are guaranteed for each contiguous 128Mb memory space.

### AC TEST CONDITION

(K9F1208X0C-XCB0 :TA=0 to 70°C, K9F1208X0C-XIB0:TA=-40 to 85°C).

| Parameter   | Value                  |                        |                         |
|---|------------------------|------------------------|-------------------------|
|   | K9F1208R0C             | K9F1208B0C             | K9F1208U0C              |
| Input Pulse Levels  | 0V to V <sub>CC</sub>  | 0V to V <sub>CC</sub>  | 0.4V to 2.4V            |
| Input Rise and Fall Times   | 5ns                    | 5ns                    | 5ns                     |
| Input and Output Timing Levels  | V <sub>CC</sub> /2     | V <sub>CC</sub> /2     | 1.5V                    |
| K9F1208R0C:Output Load (V <sub>CC</sub> :1.8V +/-10%)<br>K9F1208B0C:Output Load (V <sub>CC</sub> :2.7V +/-10%)<br>K9F1208U0C:Output Load (V <sub>CC</sub> :3.3V +/-10%) | 1 TTL GATE and CL=30pF | 1 TTL GATE and CL=30pF | 1 TTL GATE and CL=100pF |
| K9F1208U0C:Output Load (V <sub>CC</sub> :3.0V +/-10%)   | -                      | -                      | 1 TTL GATE and CL=50pF  |

### CAPACITANCE(TA=25°C, VCC=1.8V/2.7V/3.3V, f=1.0MHz)

| Item                     | Symbol           | Test Condition      | Min | Max | Unit |
|--------------------------|------------------|---------------------|-----|-----|------|
| Input/Output Capacitance | C <sub>I/O</sub> | V <sub>IL</sub> =0V | -   | 10  | pF   |
| Input Capacitance        | C <sub>IN</sub>  | V <sub>IN</sub> =0V | -   | 10  | pF   |

NOTE : Capacitance is periodically sampled and not 100% tested.

### MODE SELECTION

| CLE | ALE              | CE | WE | RE | WP                                | Mode                  |                          |
|-----|------------------|----|----|----|-----------------------------------|-----------------------|--------------------------|
| H   | L                | L  |    | H  | X                                 | Read Mode             | Command Input            |
| L   | H                | L  |    | H  | X                                 |                       | Address Input (4 clocks) |
| H   | L                | L  |    | H  | H                                 | Write Mode            | Command Input            |
| L   | H                | L  |    | H  | H                                 |                       | Address Input (4 clocks) |
| L   | L                | L  |    | H  | H                                 | Data Input            |                          |
| L   | L                | L  | H  |    | X                                 | Data Output           |                          |
| L   | L                | L  | H  | H  | X                                 | During Read (Busy)    |                          |
| X   | X                | X  | X  | X  | H                                 | During Program (Busy) |                          |
| X   | X                | X  | X  | X  | H                                 | During Erase (Busy)   |                          |
| X   | X <sup>(1)</sup> | X  | X  | X  | L                                 | Write Protect         |                          |
| X   | X                | H  | X  | X  | 0V/V <sub>CC</sub> <sup>(2)</sup> | Stand-by              |                          |

NOTE : 1. X can be V<sub>IL</sub> or V<sub>IH</sub>.

2. WP should be biased to CMOS high or CMOS low for standby.

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### Program / Erase Characteristics

| Parameter   | Symbol               | Min | Typ | Max | Unit  |
|---|----------------------|-----|-----|-----|-------|
| Program Time                                      | tPROG <sup>(1)</sup> | -   | 200 | 500 | μs    |
| Number of Partial Program Cycles in the Same Page | Main Array           | -   | -   | 1   | cycle |
|   | Spare Array          | -   | -   | 2   | cycle |
| Block Erase Time                                  | tBERS                | -   | 2   | 3   | ms    |

**NOTE NOTE:** 1. Typical Program time is defined as the time within which more than 50% of the whole pages are programmed at Vcc of 3.3V and 25°C

### AC TIMING CHARACTERISTICS FOR COMMAND / ADDRESS / DATA INPUT

| Parameter                             | Symbol             | Min | Max | Unit |
|---------------------------------------|--------------------|-----|-----|------|
| CLE setup Time                        | tCLS               | 21  | -   | ns   |
| CLE Hold Time                         | tCLH               | 5   | -   | ns   |
| $\overline{\text{CE}}$ setup Time     | tCS                | 31  | -   | ns   |
| $\overline{\text{CE}}$ Hold Time      | tCH                | 5   | -   | ns   |
| WE Pulse Width                        | tWP <sup>(1)</sup> | 21  | -   | ns   |
| ALE setup Time                        | tALS               | 21  | -   | ns   |
| ALE Hold Time                         | tALH               | 5   | -   | ns   |
| Data setup Time                       | tDS                | 20  | -   | ns   |
| Data Hold Time                        | tDH                | 5   | -   | ns   |
| Write Cycle Time                      | tWC                | 42  | -   | ns   |
| $\overline{\text{WE}}$ High Hold Time | tWH                | 15  | -   | ns   |

**NOTE:** The transition of the corresponding control pins must occur only once while  $\overline{\text{WE}}$  is held low.



# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### AC CHARACTERISTICS FOR OPERATION

| Parameter  | Symbol               | Min | Max                     | Unit |
|--|----------------------|-----|-------------------------|------|
| Data Transfer from Cell to Register                    | tR                   | -   | 15                      | μs   |
| ALE to $\overline{RE}$ Delay                           | tAR                  | 10  | -                       | ns   |
| CLE to $\overline{RE}$ Delay                           | tCLR                 | 10  | -                       | ns   |
| Ready to $\overline{RE}$ Low                           | tRR                  | 20  | -                       | ns   |
| RE Pulse Width   | tRP                  | 21  | -                       | ns   |
| WE High to Busy  | tWB                  | -   | 100                     | ns   |
| Read Cycle Time  | tRC                  | 42  | -                       | ns   |
| $\overline{RE}$ Access Time                            | tREA                 | -   | 30                      | ns   |
| $\overline{CE}$ Access Time                            | tCEA                 | -   | 35                      | ns   |
| $\overline{RE}$ High to Output Hi-Z                    | tRHZ                 | -   | 30                      | ns   |
| $\overline{CE}$ High to Output Hi-Z                    | tCHZ                 | -   | 20                      | ns   |
| $\overline{CE}$ High to ALE or CLE Don't Care          | tCSD                 | 10  | -                       | ns   |
| $\overline{RE}$ or $\overline{CE}$ High to Output hold | tOH                  | 15  | -                       | ns   |
| $\overline{RE}$ High Hold Time                         | tREH                 | 15  | -                       | ns   |
| Output Hi-Z to $\overline{RE}$ Low                     | tIR                  | 0   | -                       | ns   |
| WE High to $\overline{RE}$ Low                         | tWHR                 | 60  | -                       | ns   |
| Device resetting time(Read/Program/Erase)              | tRST                 | -   | 5/10/500 <sup>(1)</sup> | μs   |
| RE Pulse Width during Busy State                       | tRPB <sup>(2)</sup>  | 35  | -                       | ns   |
| Read Cycle Time during Busy State                      | tRCB <sup>(2)</sup>  | 50  | -                       | ns   |
| $\overline{RE}$ Access Time during Busy State          | tREAB <sup>(2)</sup> | -   | 40                      | ns   |

| Parameter         |   | Symbol | Min | Max | Uni     |
|-------------------|---|--------|-----|-----|---------|
| K9F1208X0C-P only | Last RE High to Busy(at sequential read)  | tRB    | -   | 100 | ns      |
|                   | $\overline{CE}$ High to Ready(in case of interception by $\overline{CE}$ at read) | tCRY   | -   | 5   | $\mu$ s |
|                   | $\overline{CE}$ High Hold Time(at the last serial read) <sup>(4)</sup>            | tCEH   | 100 | -   | ns      |

**NOTE:** 1. If reset command(FFh) is written at Ready state, the device goes into Busy for maximum 5us.  
 2. This parameter (tRPB/tRCB/tREAB) must be used only for 1.8V device.  
 3. The time to Ready depends on the value of the pull-up resistor tied R/B pin.

## NAND Flash Technical Notes

### Initial Invalid Block(s)

Initial invalid blocks are defined as blocks that contain one or more initial invalid bits whose reliability is not guaranteed by Samsung. The information regarding the initial invalid block(s) is so called as the initial invalid block information. Devices with initial invalid block(s) have the same quality level as devices with all valid blocks and have the same AC and DC characteristics. An initial invalid block(s) does not affect the performance of valid block(s) because it is isolated from the bit line and the common source line by a select transistor. The system design must be able to mask out the initial invalid block(s) via address mapping. The 1st block, which is placed on 00h block address, is guaranteed to be a valid block up to 1K program/erase cycles with 1bit/512Byte ECC.

### Identifying Initial Invalid Block(s)

All device locations are erased(FFh) except locations where the initial invalid block(s) information is written prior to shipping. The initial invalid block(s) status is defined by the 6th byte in the spare area. Samsung makes sure that either the 1st or 2nd page of every initial invalid block has non-FFh data at the column address of 517. Since the initial invalid block information is also erasable in most cases, it is impossible to recover the information once it has been erased. Therefore, the system must be able to recognize the initial invalid block(s) based on the initial invalid block information and create the initial invalid block table via the following suggested flow chart(Figure 3). Any intentional erasure of the initial invalid block information is prohibited.

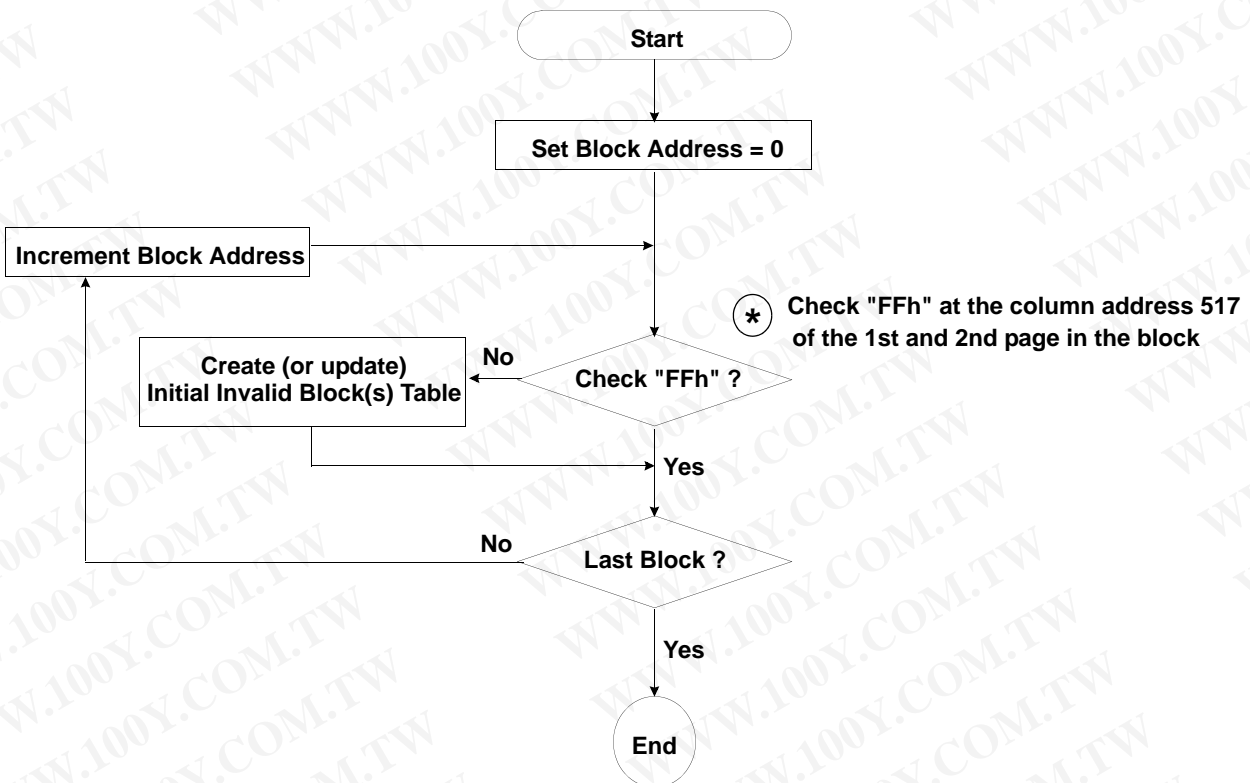


Figure 3. Flow chart to create initial invalid block table.

# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### NAND Flash Technical Notes (Continued)

#### Error in write or read operation

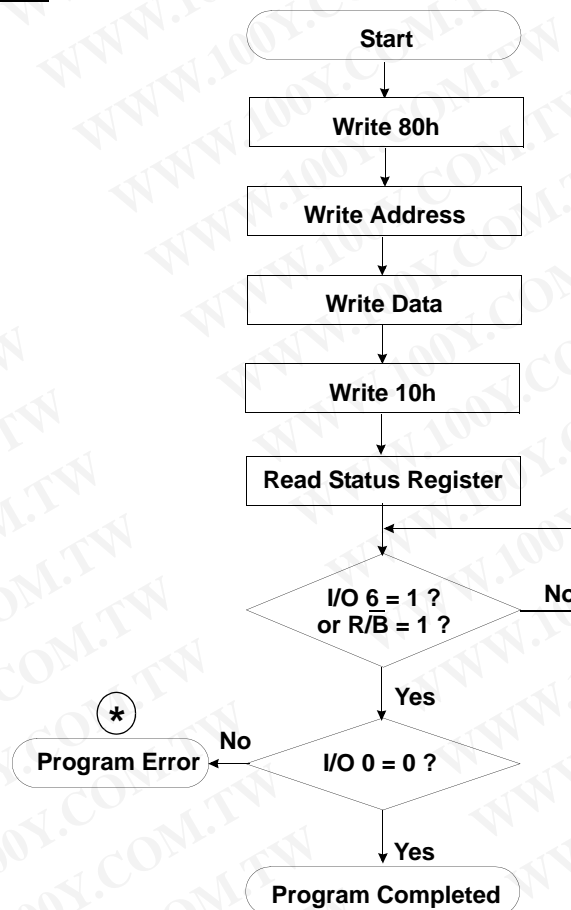
Within its life time, the additional invalid blocks may develop with NAND Flash memory. Refer to the qualification report for the block failure rate. The following possible failure modes should be considered to implement a highly reliable system. In the case of status read failure after erase or program, block replacement should be done. Because program status fail during a page program does not affect the data of the other pages in the same block, block replacement can be executed with a page-sized buffer by finding an erased empty block and reprogramming the current target data and copying the rest of the replaced block. In case of Read, ECC must be employed. To improve the efficiency of memory space, it is recommended that the read failure due to single bit error should be reclaimed by ECC without any block replacement. The block failure rate in the qualification report does not include those reclaimed blocks.

|       | Failure Mode       | Detection and Countermeasure sequence           |
|-------|--------------------|---|
| Write | Erase Failure      | Status Read after Erase --> Block Replacement   |
|       | Program Failure    | Status Read after Program --> Block Replacement |
| Read  | Single Bit Failure | Verify ECC -> ECC Correction                    |

#### ECC

: Error Correcting Code --> Hamming Code etc.  
 Example) 1bit correction & 2bits detection

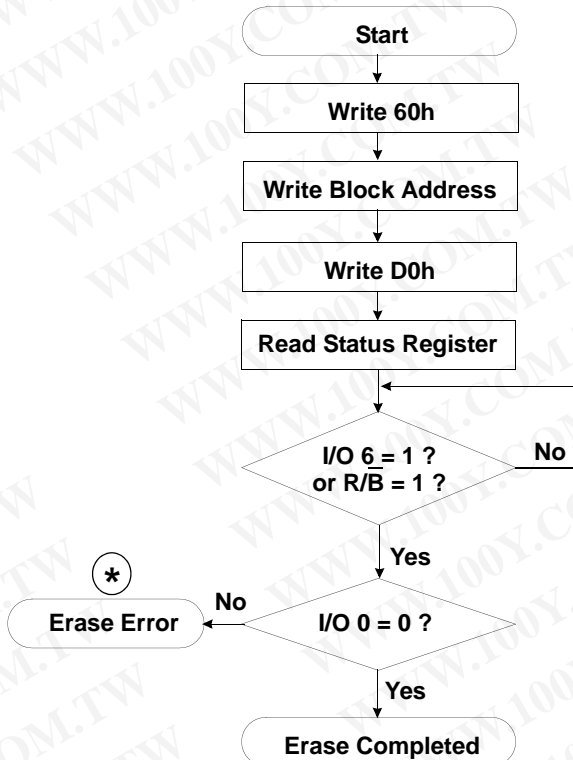
#### Program Flow Chart



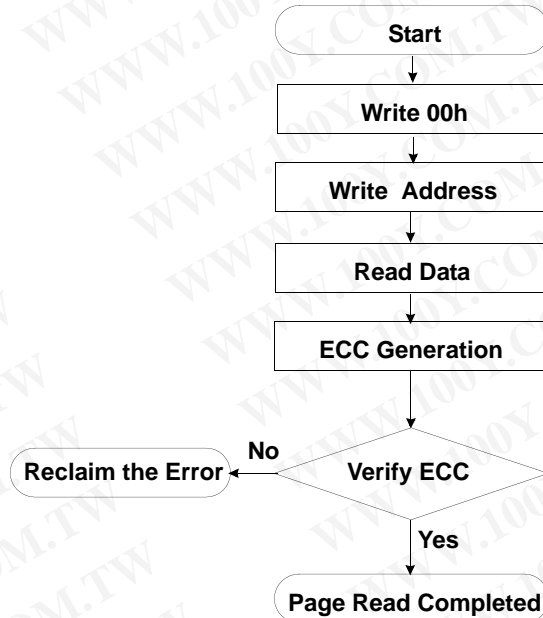
(\*) : If program operation results in an error, map out the block including the page in error and copy the target data to another block.

**NAND Flash Technical Notes (Continued)**

**Erase Flow Chart**

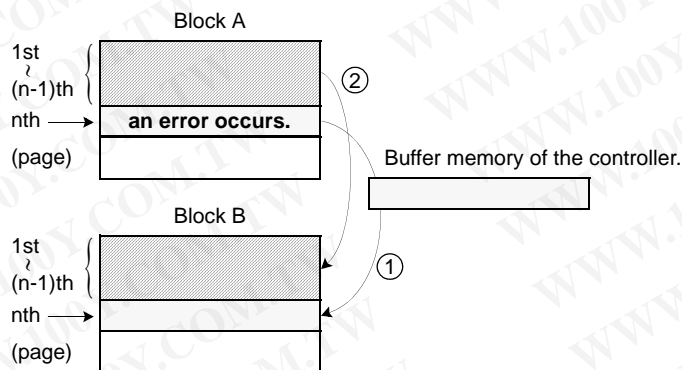


**Read Flow Chart**



\* : If erase operation results in an error, map out the failing block and replace it with another block.

**Block Replacement**



- \* Step1. When an error happens in the nth page of the Block 'A' during erase or program operation.
- \* Step2. Copy the nth page data of the Block 'A' in the buffer memory to the nth page of another free block. (Block 'B')
- \* Step3. Then, copy the data in the 1st ~ (n-1)th page to the same location of the Block 'B'.
- \* Step4. Do not further erase Block 'A' by creating an 'invalid Block' table or other appropriate scheme.



# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### Pointer Operation of K9F1208X0C

Samsung NAND Flash has three address pointer commands as a substitute for the two most significant column addresses. '00h' command sets the pointer to 'A' area(0~255byte), '01h' command sets the pointer to 'B' area(256~511byte), and '50h' command sets the pointer to 'C' area(512~527byte). With these commands, the starting column address can be set to any of a whole page(0~527byte). '00h' or '50h' is sustained until another address pointer command is inputted. '01h' command, however, is effective only for one operation. After any operation of Read, Program, Erase, Reset, Power\_Up is executed once with '01h' command, the address pointer returns to 'A' area by itself. To program data starting from 'A' or 'C' area, '00h' or '50h' command must be inputted before '80h' command is written. A complete read operation prior to '80h' command is not necessary. To program data starting from 'B' area, '01h' command must be inputted right before '80h' command is written.

Table 2. Destination of the pointer

| Command | Pointer position | Area              |
|---------|------------------|-------------------|
| 00h     | 0 ~ 255 byte     | 1st half array(A) |
| 01h     | 256 ~ 511 byte   | 2nd half array(B) |
| 50h     | 512 ~ 527 byte   | spare array(C)    |

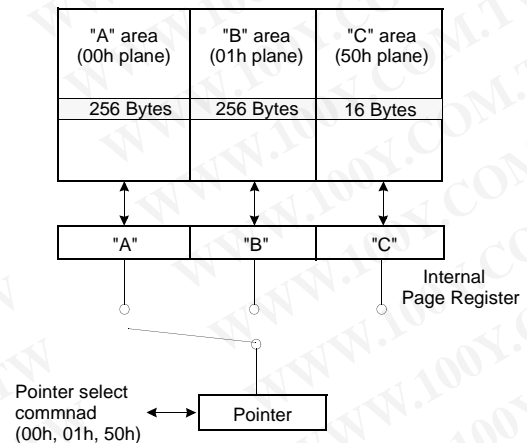
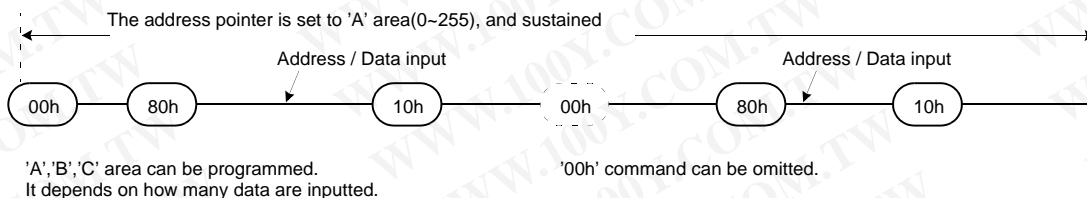
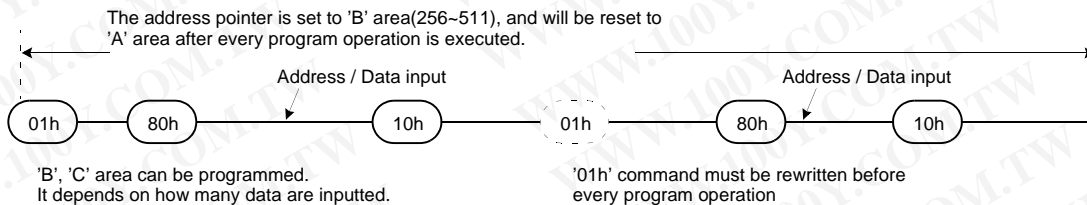


Figure 4. Block Diagram of Pointer Operation

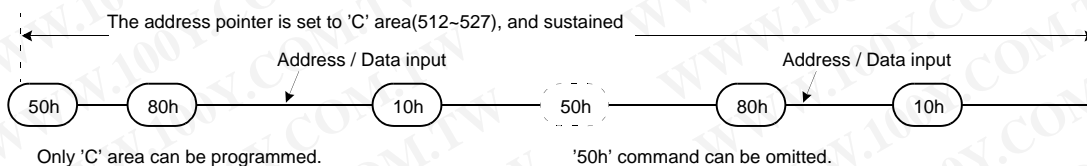
#### (1) Command input sequence for programming 'A' area



#### (2) Command input sequence for programming 'B' area



#### (3) Command input sequence for programming 'C' area



# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### System Interface Using $\overline{CE}$ don't-care.

For an easier system interface,  $\overline{CE}$  may be inactive during the data-loading or sequential data-reading as shown below. The internal 528bytes page registers are utilized as separate buffers for this operation and the system design gets more flexible. In addition, for voice or audio applications which use slow cycle time on the order of u-seconds, de-activating  $\overline{CE}$  during the data-loading and reading would provide significant savings in power consumption.

Figure 5. Program Operation with  $\overline{CE}$  don't-care.

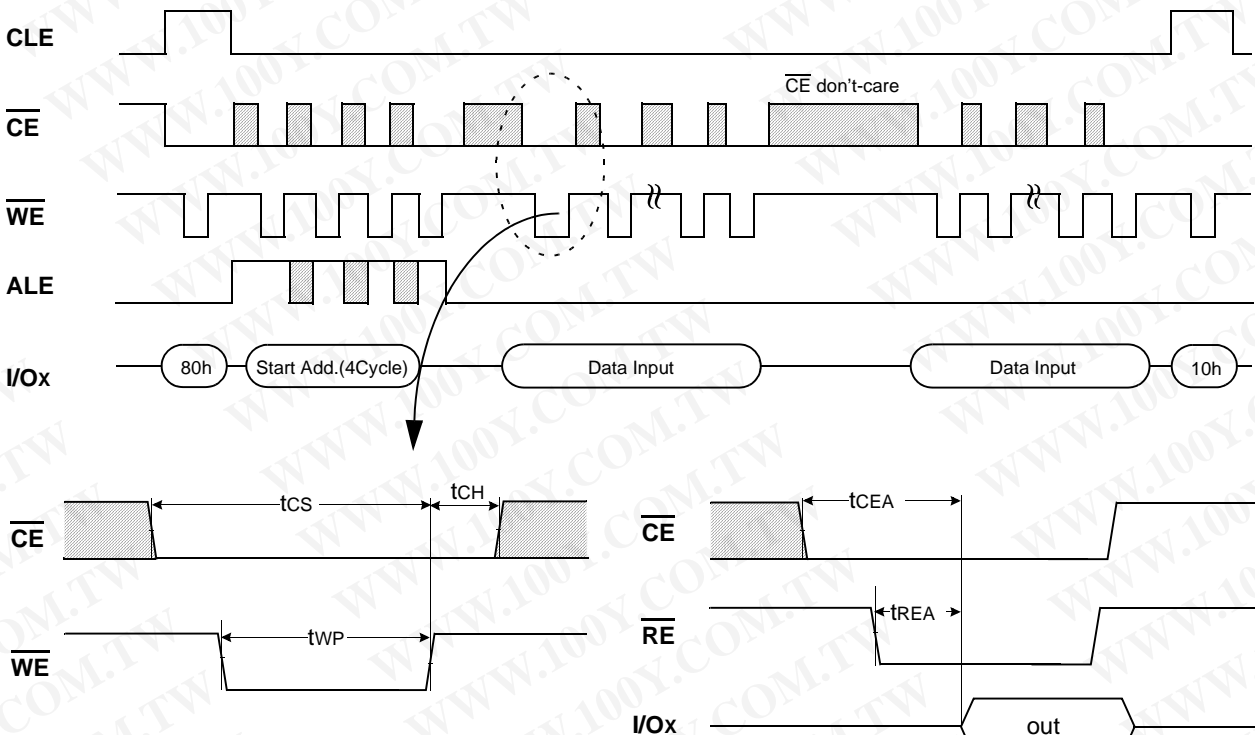
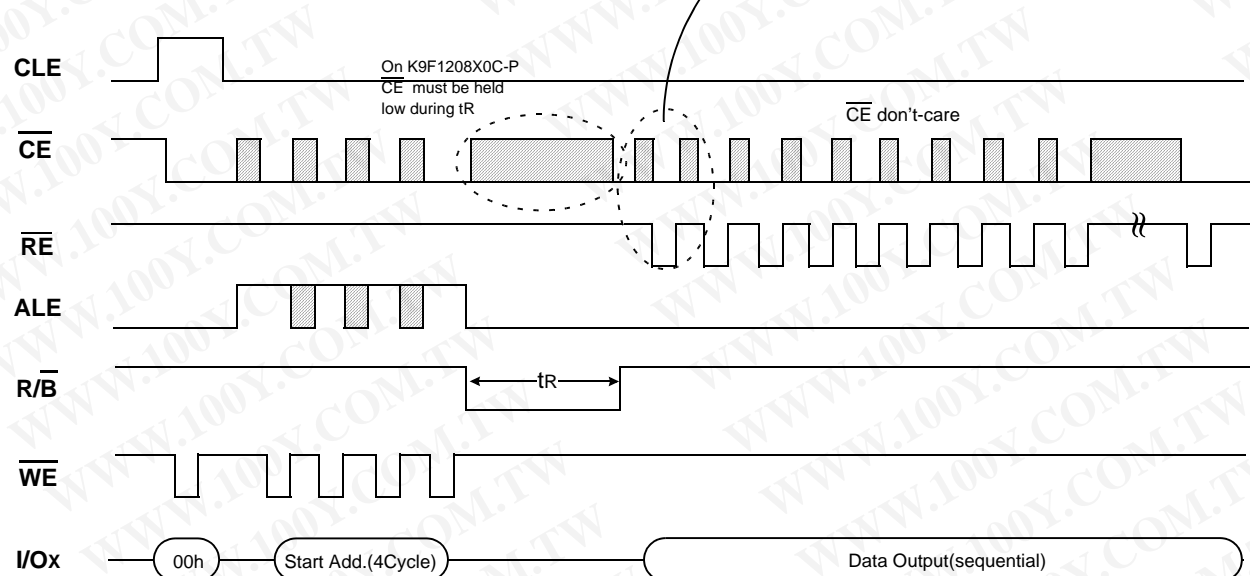


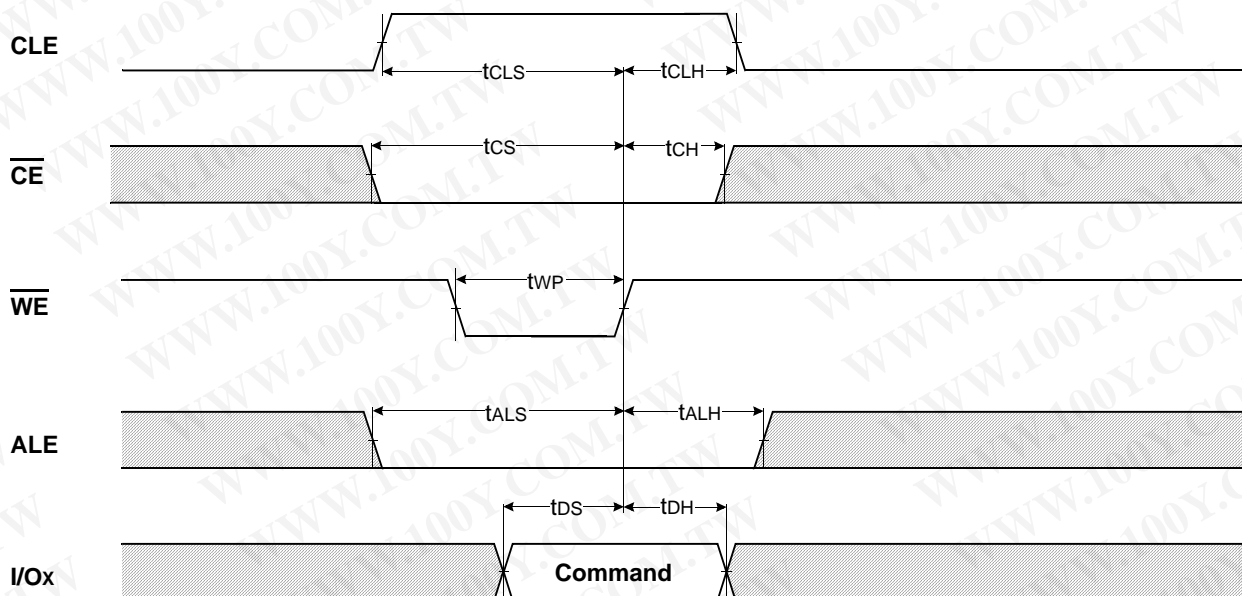
Figure 6. Read Operation with  $\overline{CE}$  don't-care.



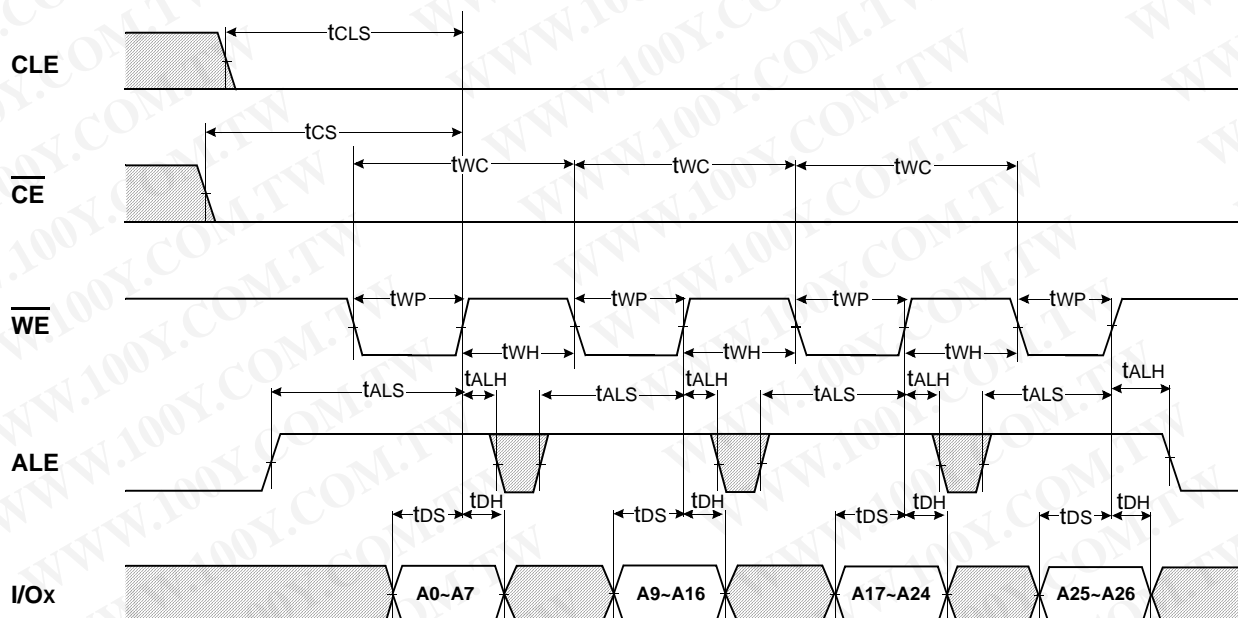
# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### \* Command Latch Cycle



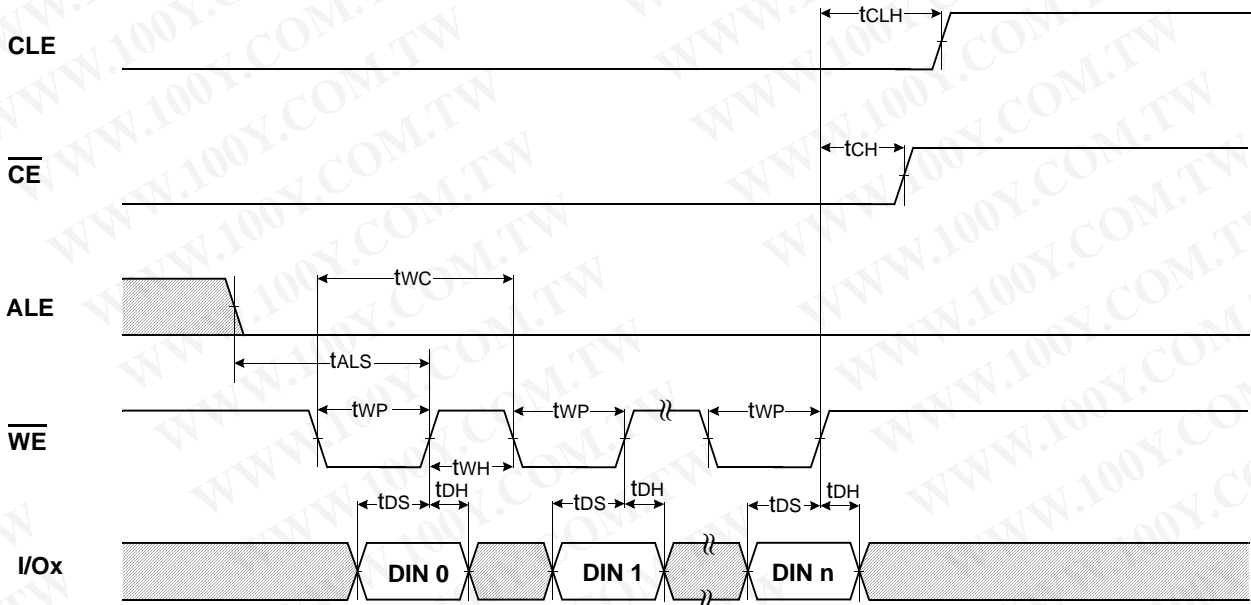
### \* Address Latch Cycle



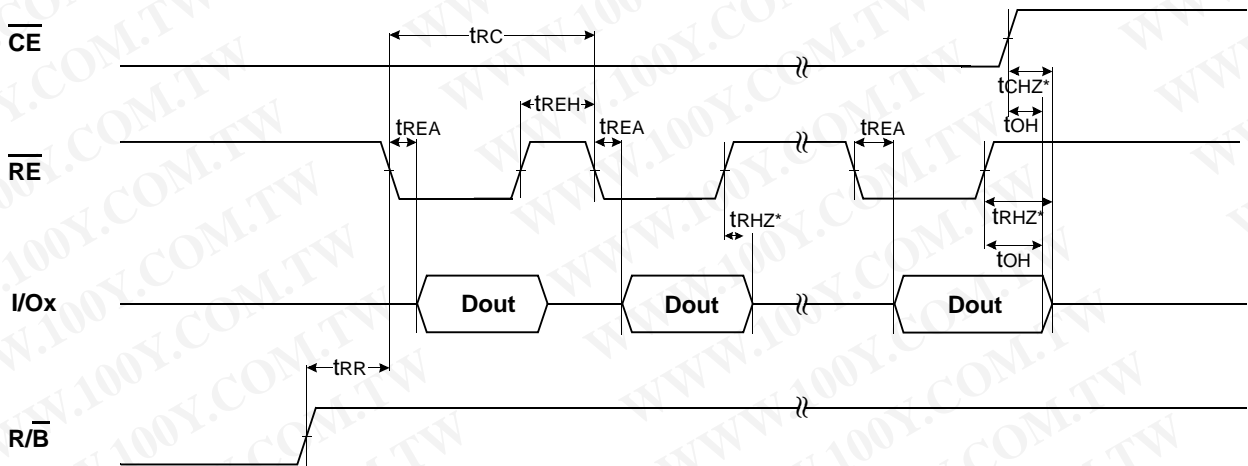
**K9F1208U0C**  
**K9F1208R0C K9F1208B0C**

**FLASH MEMORY**

**\* Input Data Latch Cycle**



**\* Serial access Cycle after Read (CLE=L,  $\overline{\text{WE}}$ =H, ALE=L)**



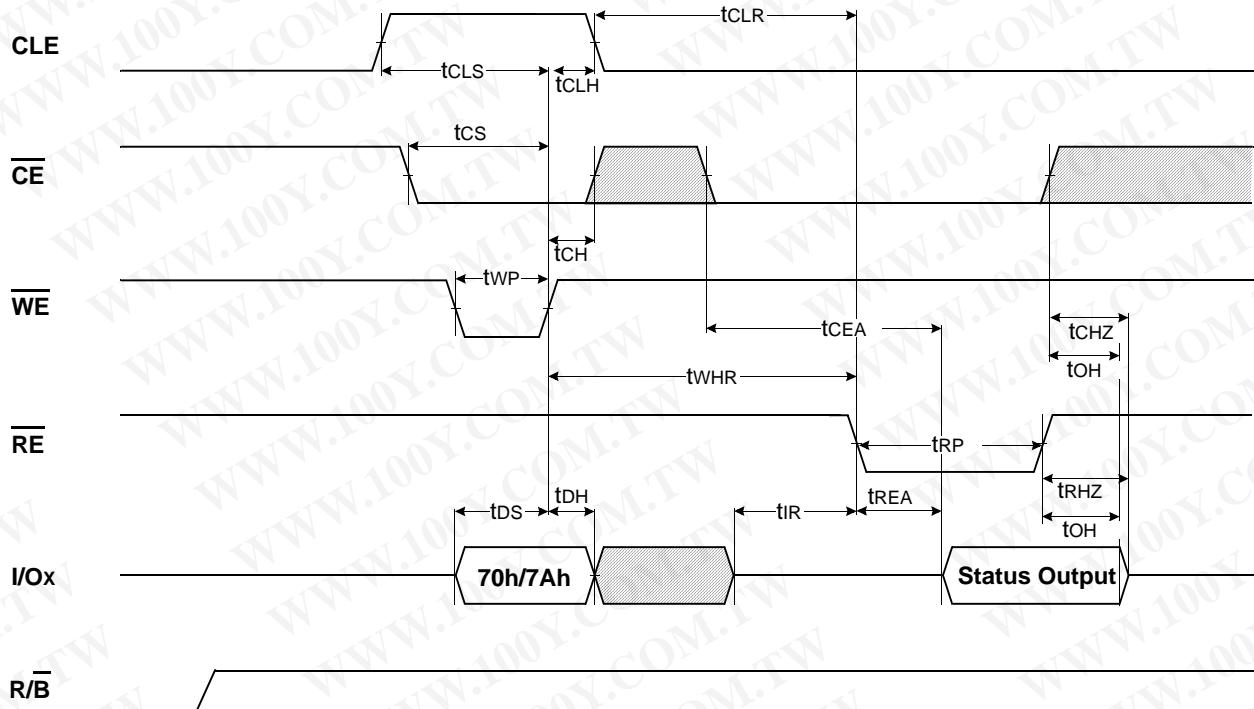
**NOTES :** Transition is measured  $\pm 200\text{mV}$  from steady state voltage with load.  
 This parameter is sampled and not 100% tested.



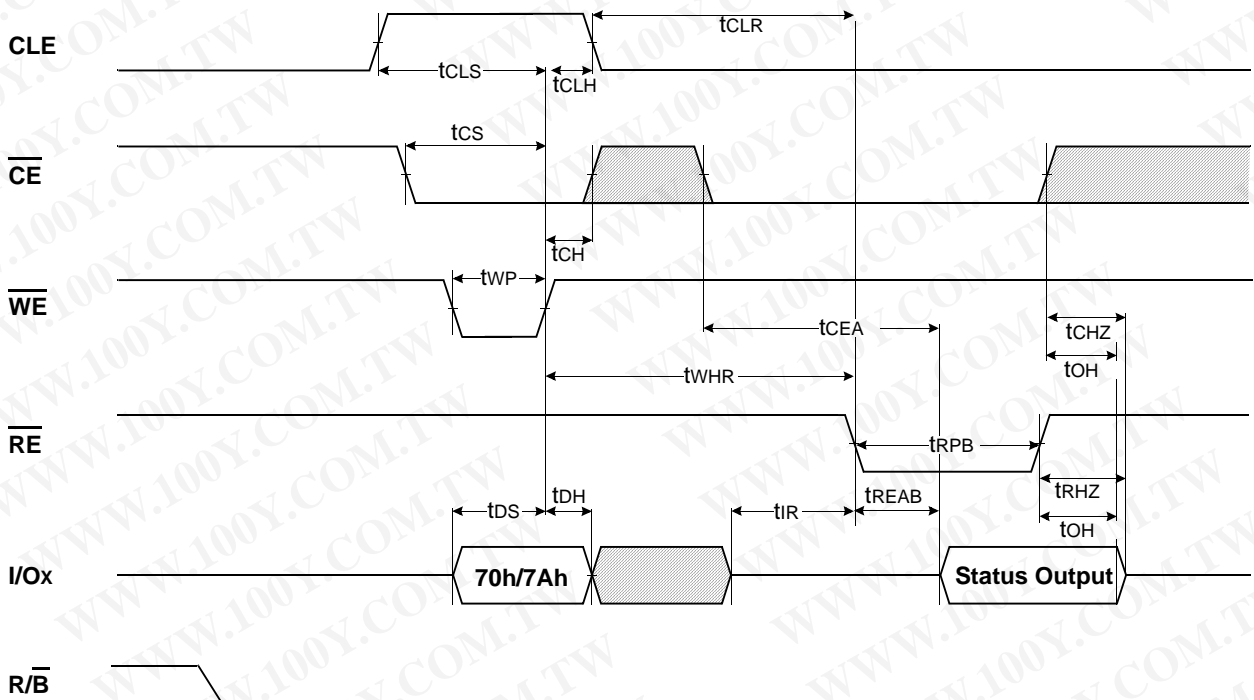
**K9F1208U0C**  
**K9F1208R0C K9F1208B0C**

**FLASH MEMORY**

**Status Read Cycle (During Ready State)**



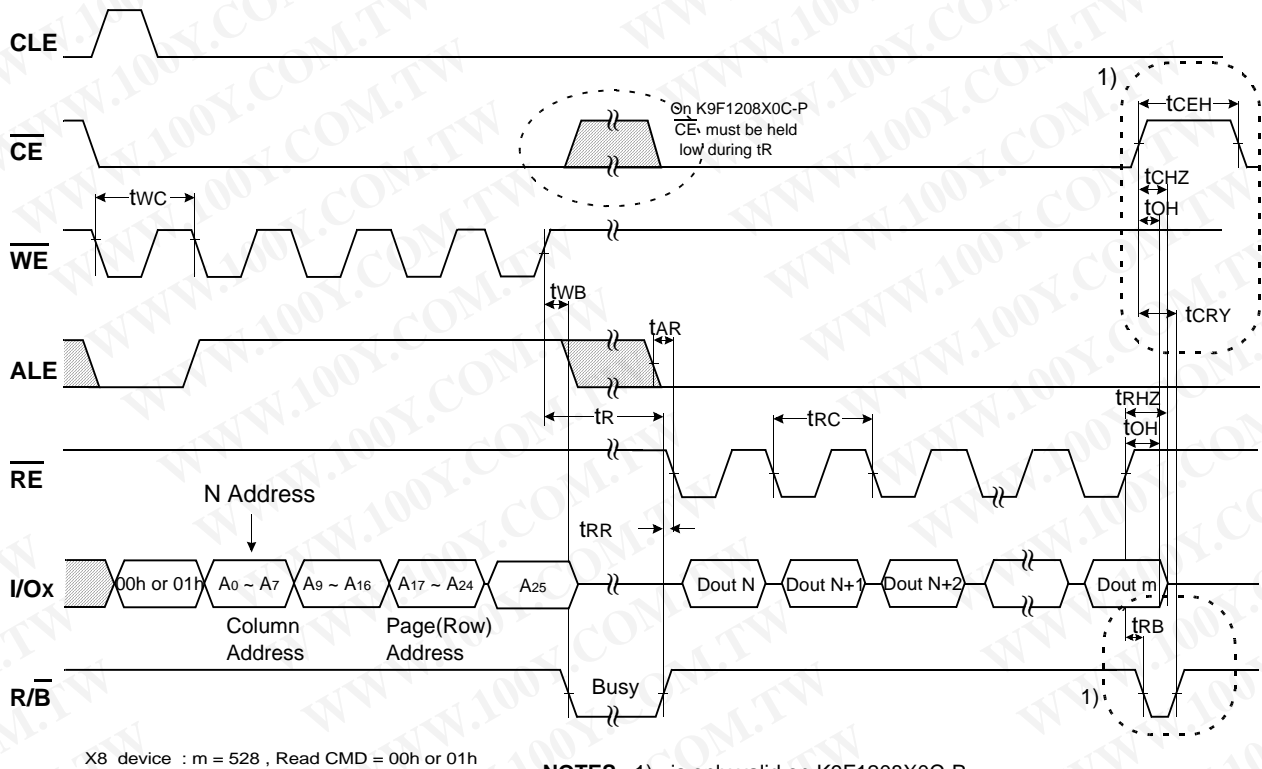
**Status Read Cycle (During Busy State)**



# K9F1208U0C K9F1208R0C K9F1208B0C

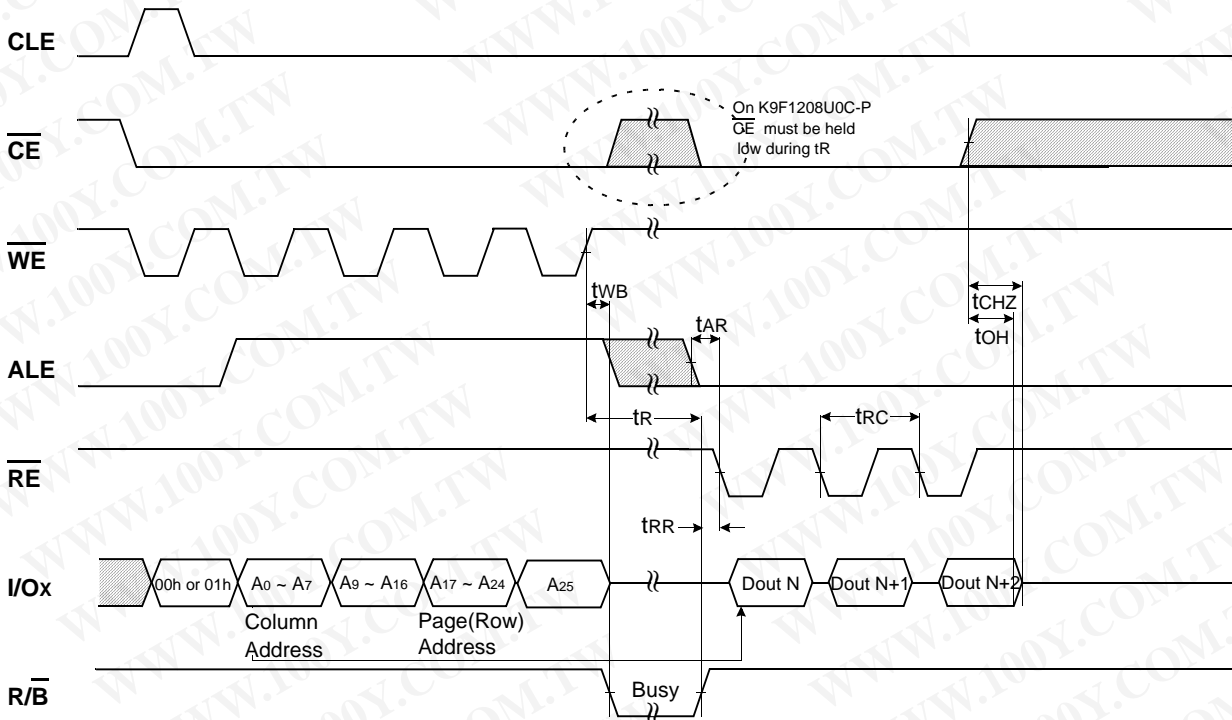
## FLASH MEMORY

### READ1 OPERATION (READ ONE PAGE)



NOTES : 1) is only valid on K9F1208X0C-P

### Read1 Operation (Intercepted by $\overline{CE}$ )

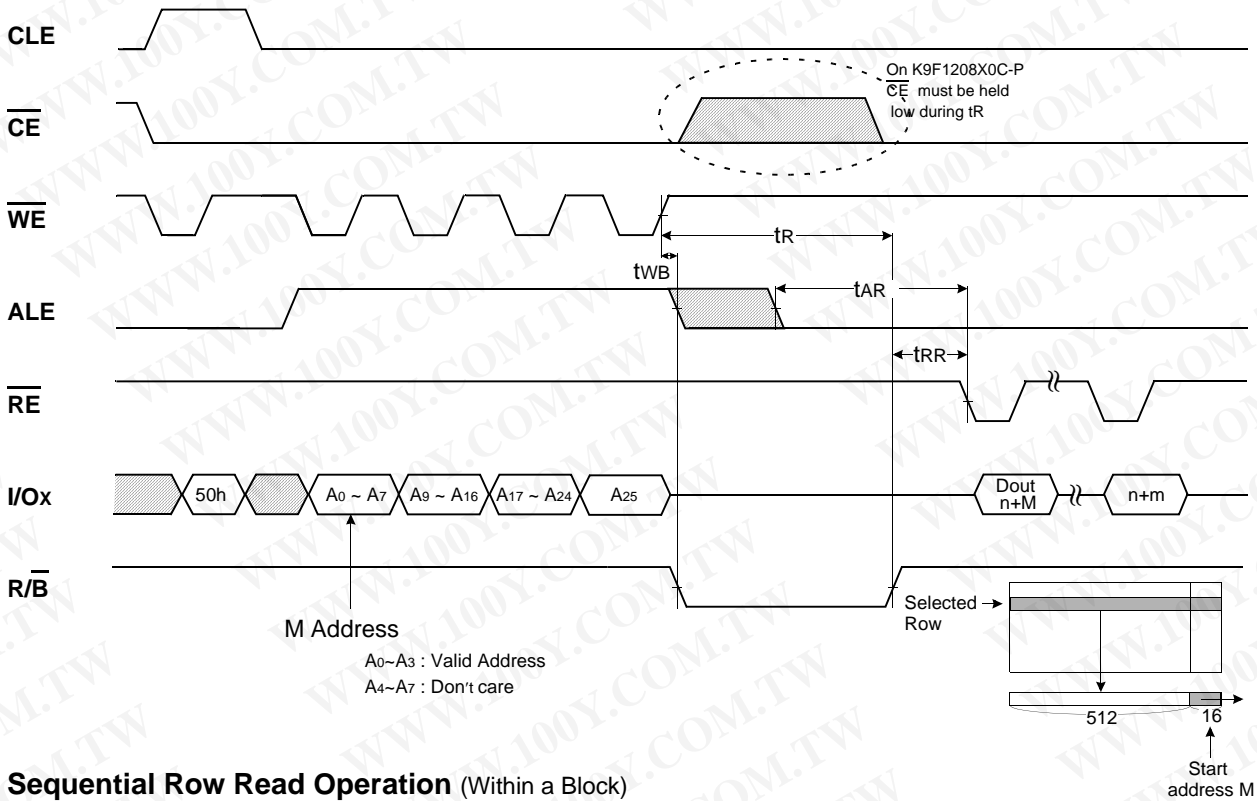


# K9F1208U0C K9F1208R0C K9F1208B0C

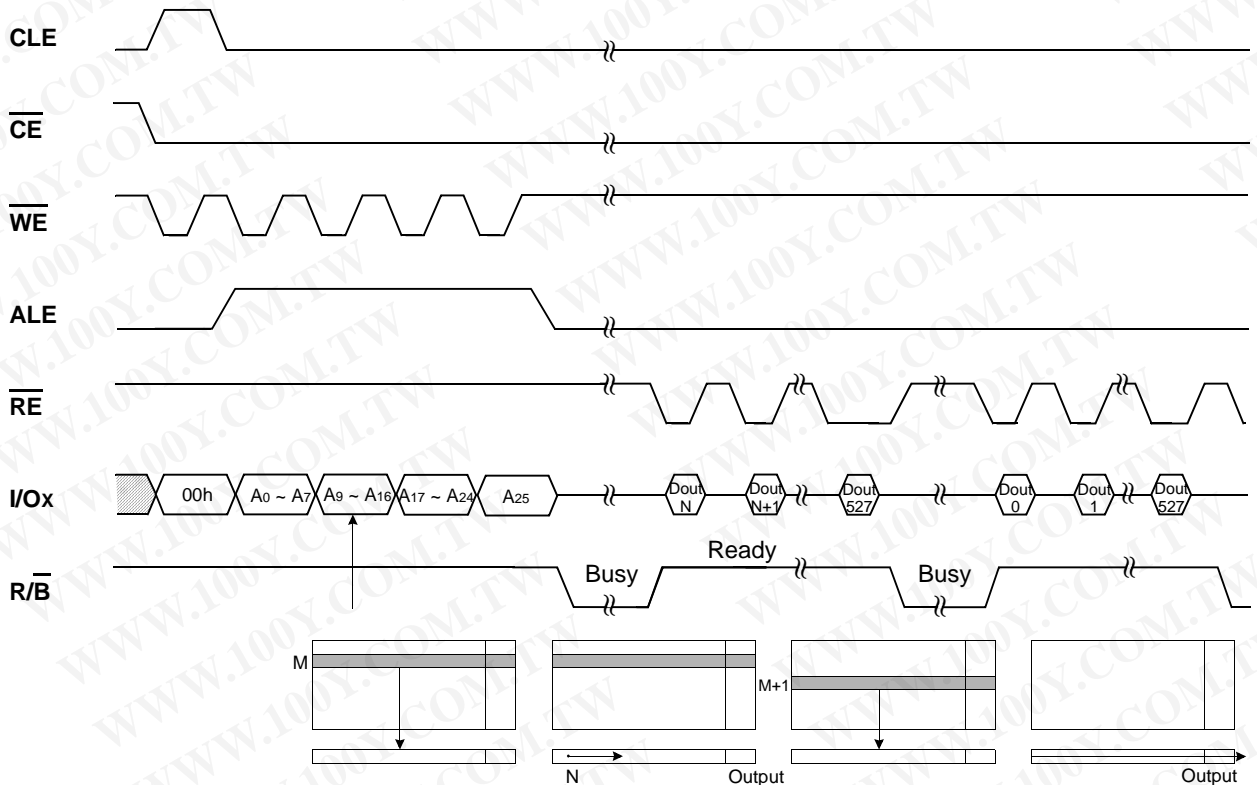
勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
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## FLASH MEMORY

### Read2 Operation (Read One Page)



### Sequential Row Read Operation (Within a Block)

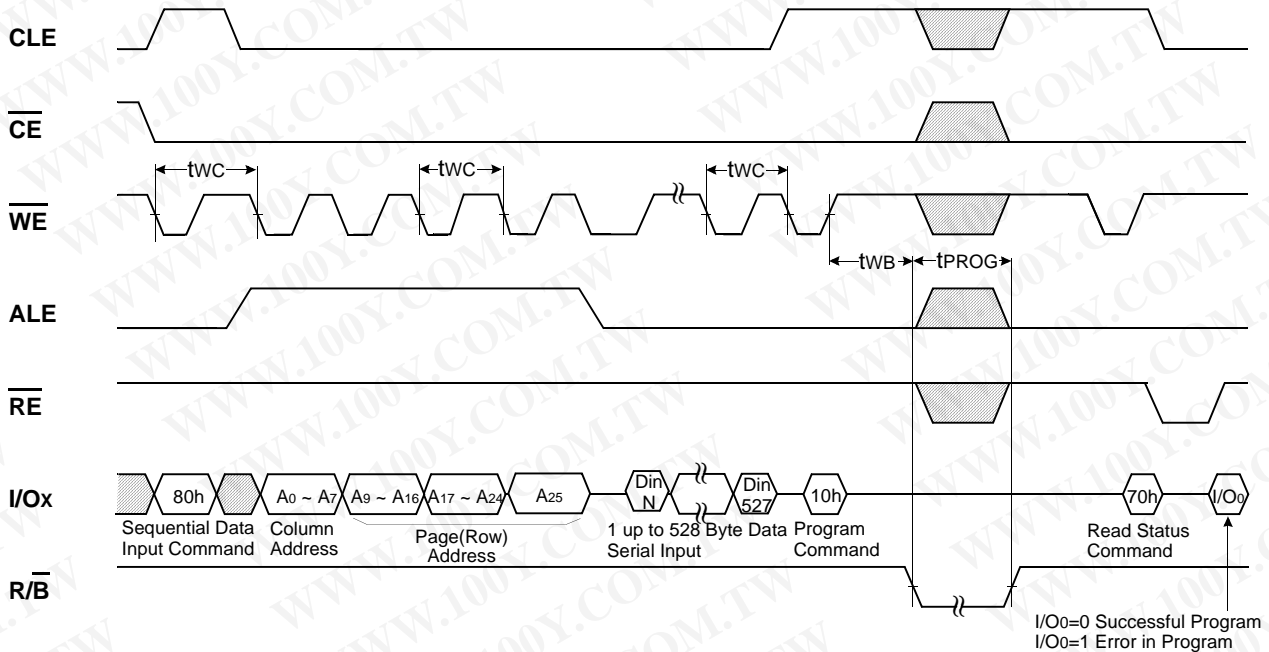


**K9F1208U0C**  
**K9F1208R0C K9F1208B0C**

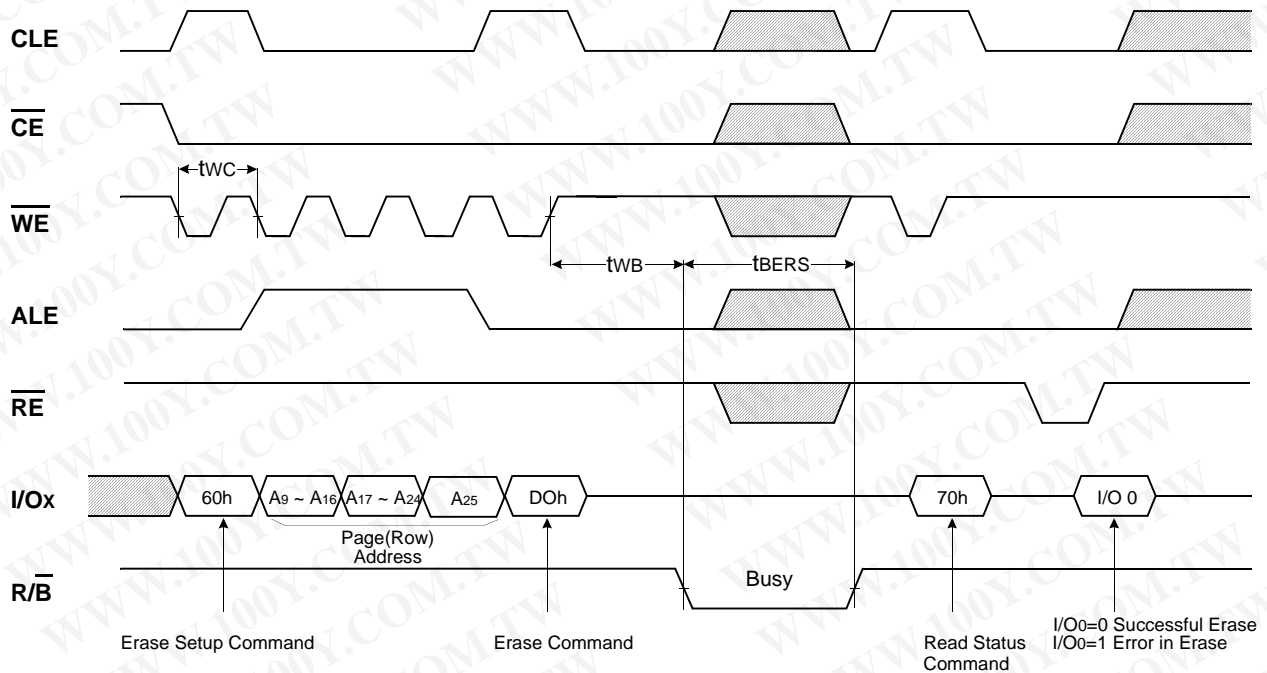
勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-34970699  
 勝特力电子(深圳) 86-755-83298787  
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**FLASH MEMORY**

**Page Program Operation**



**Block Erase Operation (Erase One Block)**

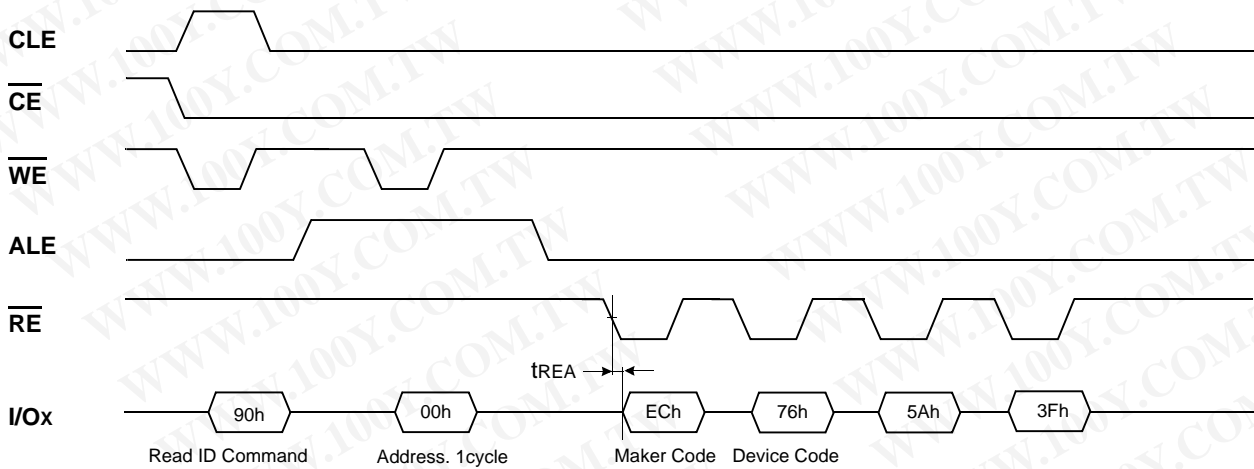




# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### Read ID Operation



### ID Defintition Table

90 ID : Access command = 90H

|                      | Value | Description                         |
|----------------------|-------|-------------------------------------|
| 1 <sup>st</sup> Byte | ECh   | Maker Code                          |
| 2 <sup>nd</sup> Byte | 76h   | Device Code                         |
| 3 <sup>rd</sup> Byte | 5Ah   | Don't support Copy Back Operation   |
| 4 <sup>th</sup> Byte | 3Fh   | Don't support Multi Plane Operation |

## K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### Device Operation

#### PAGE READ

Upon initial device power up, the device defaults to Read1 mode. This operation is also initiated by writing 00h to the command register along with four address cycles. Once the command is latched, it does not need to be written for the following page read operation. Three types of operations are available : random read, serial page read and sequential row read.

The random read mode is enabled when the page address is changed. The 528 bytes of data within the selected page are transferred to the data registers in less than 15 $\mu$ s(tr). The system controller can detect the completion of this data transfer(tr) by analyzing the output of R/B pin.  $\overline{CE}$  must be held low while in busy for K9F1208X0C-PXB0, while  $\overline{CE}$  is don't-care with K9F1208X0C-JXB0. If  $\overline{CE}$  goes high before the device returns to Ready, the random read operation is interrupted and Busy returns to Ready as the defined by tCRY. Since the operation was aborted, the serial page read does not output valid data. Once the data in a page is loaded into the registers, they may be read out in 42ns cycle time by sequentially pulsing RE. High to low transitions of the RE clock output the data starting from the selected column address up to the last column address.

The way the Read1 and Read2 commands work is like a pointer set to either the main area or the spare area. The spare area of 512 to 527 bytes may be selectively accessed by writing the Read2 command. Addresses A0 to A3 set the starting address of the spare area while addresses A4 to A7 are ignored. The Read1 command(00h/01h) is needed to move the pointer back to the main area. Figures 7 to 10 show typical sequence and timings for each read operation.

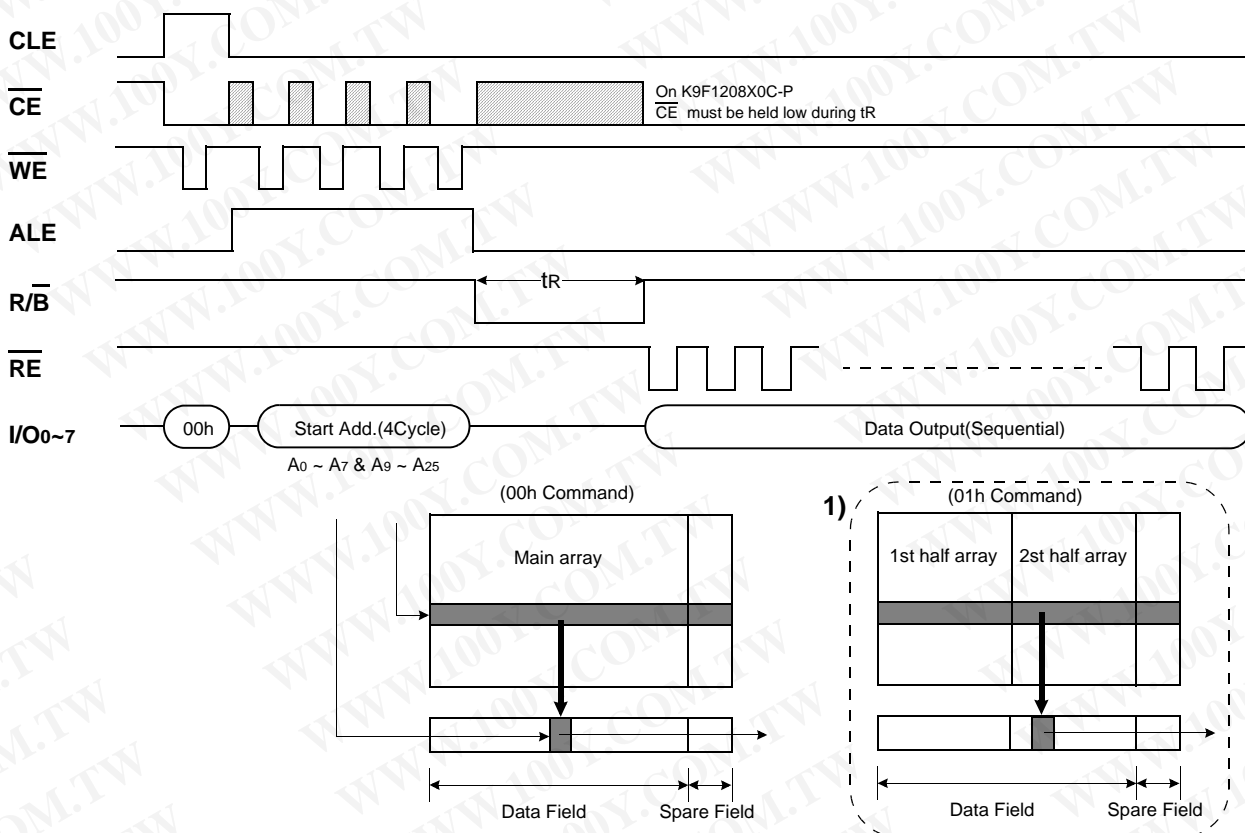
#### Sequential Row Read is available only on K9F1208X0C-P :

After the data of last column address is clocked out, the next page is automatically selected for sequential row read. Waiting 15 $\mu$ s again allows reading the selected page. The sequential row read operation is terminated by bringing  $\overline{CE}$  high. Unless the operation is aborted, the page address is automatically incremented for sequential row read as in Read1 operation and spare sixteen bytes of each page may be sequentially read. The Sequential Read 1 and 2 operation is allowed only within a block and after the last page of a block is readout, the sequential read operation must be terminated by bringing  $\overline{CE}$  high. When the page address moves onto the next block, read command and address must be given. Figures 9, 10 show typical sequence and timings for sequential row read operation.

# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

Figure 7. Read1 Operation



### NOTE :

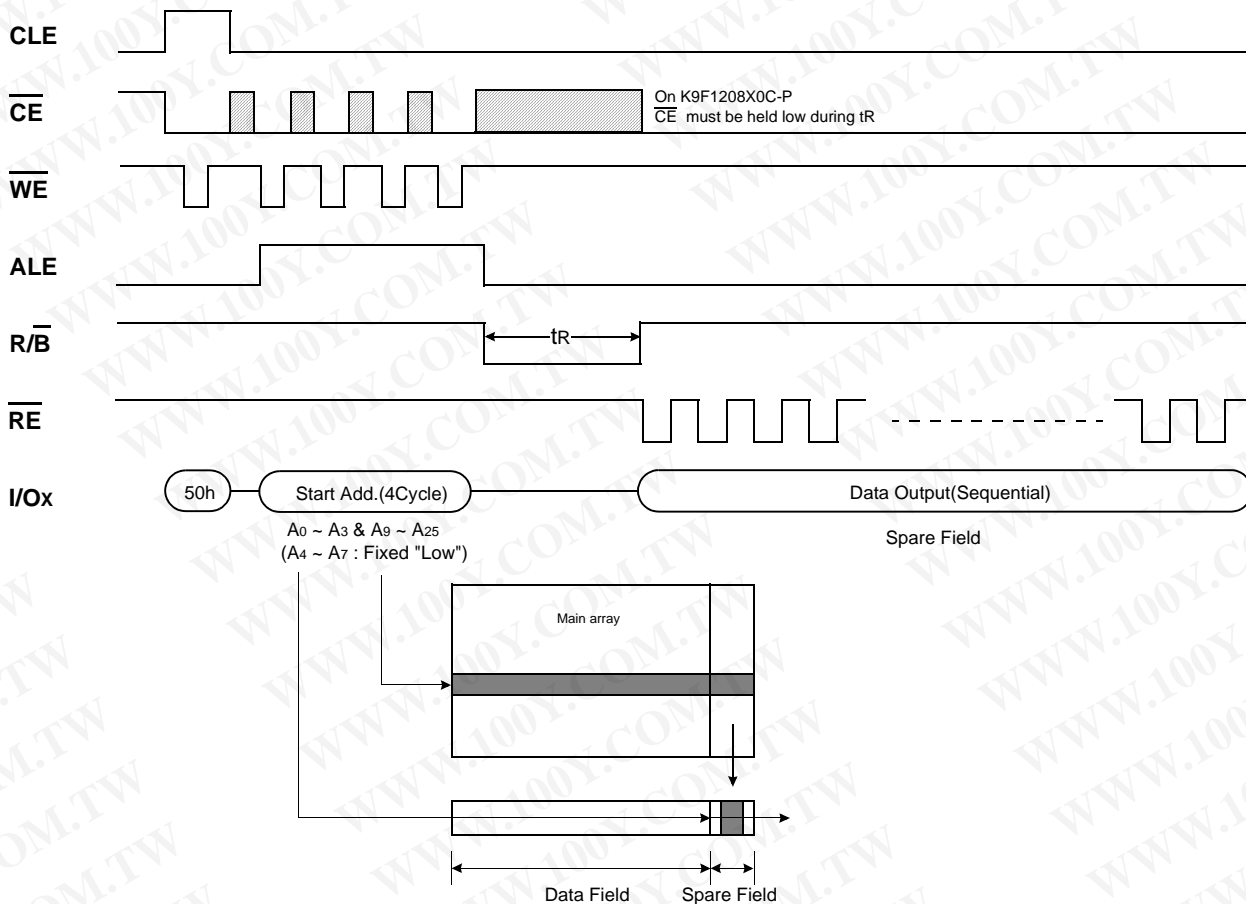
- 1) After data access on 2nd half array by 01h command, the start pointer is automatically moved to 1st half array (00h) at next cycle.

# K9F1208U0C K9F1208R0C K9F1208B0C

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## FLASH MEMORY

Figure 8. Read2 Operation

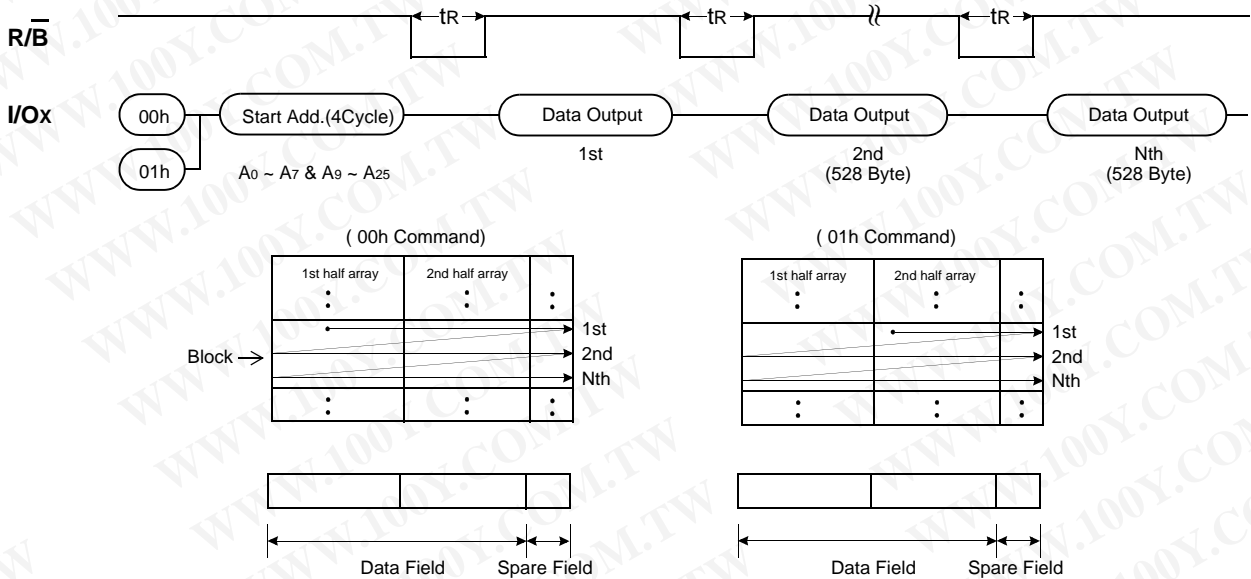




**K9F1208U0C**  
**K9F1208R0C K9F1208B0C**

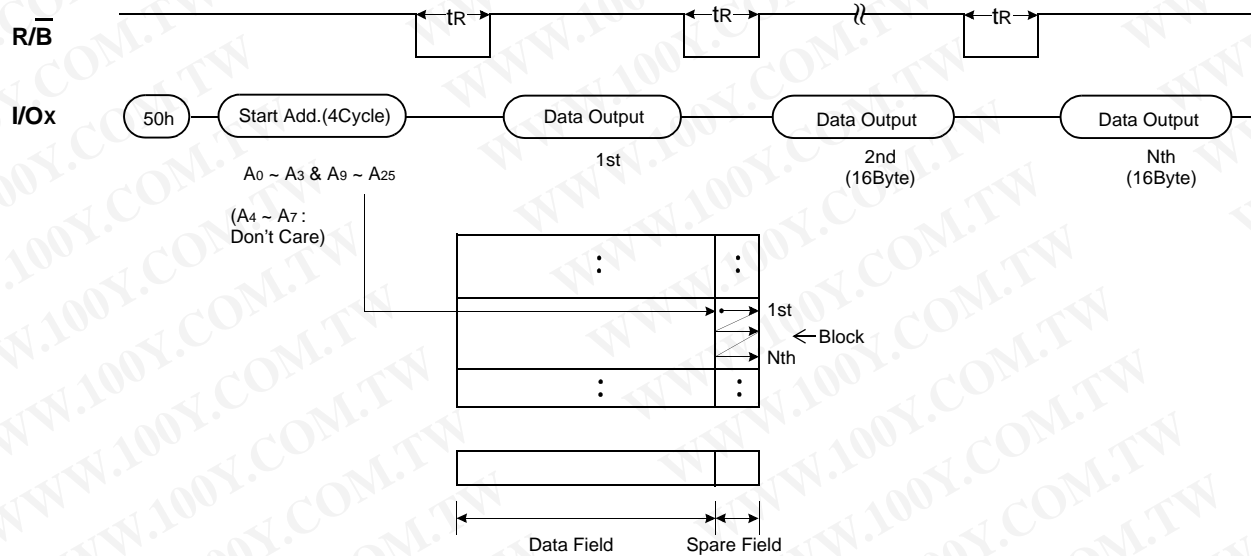
**FLASH MEMORY**

**Figure 9. Sequential Row Read1 Operation** (only for K9F1208X0C-P valid within a block)



The Sequential Read 1 and 2 operation is allowed only within a block and after the last page of a block is read-out, the sequential read operation must be terminated by bringing CE high. When the page address moves onto the next block, read command and address must be given.

**Figure 10. Sequential Row Read2 Operation** (only for K9F1208X0C-P valid within a block)



# K9F1208U0C K9F1208R0C K9F1208B0C

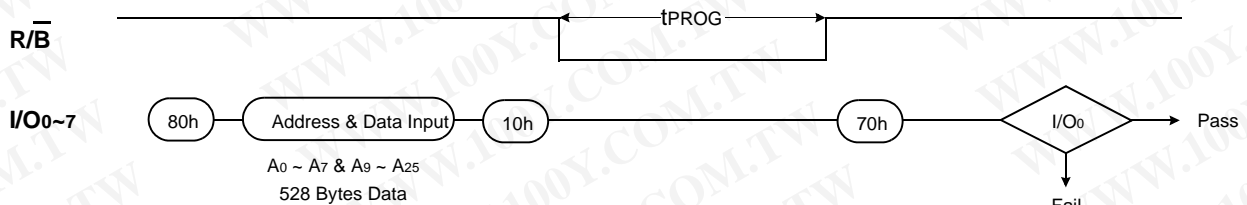
## FLASH MEMORY

### PAGE PROGRAM

The device is programmed basically on a page basis, but it does allow multiple partial page programming of a byte or consecutive bytes up to 528 byte, in a single page program cycle. The number of consecutive partial page programming operation within the same page without an intervening erase operation must not exceed 1 for main array and 2 for spare array. The addressing may be done in any random order in a block. A page program cycle consists of a serial data loading period in which up to 528 bytes of data may be loaded into the page register, followed by a non-volatile programming period where the loaded data is programmed into the appropriate cell. Serial data loading can be started from 2nd half array by moving pointer. About the pointer operation, please refer to the attached technical notes.

The serial data loading period begins by inputting the Serial Data Input command(80h), followed by the four cycle address input and then serial data loading. The bytes other than those to be programmed do not need to be loaded. The Page Program confirm command(10h) initiates the programming process. Writing 10h alone without previously entering the serial data will not initiate the programming process. The internal write state control automatically executes the algorithms and timings necessary for program and verify, thereby freeing the system controller for other tasks. Once the program process starts, the Read Status Register command may be entered, with RE and CE low, to read the status register. The system controller can detect the completion of a program cycle by monitoring the R/B output, or the Status bit(I/O 6) of the Status Register. Only the Read Status command and Reset command are valid while programming is in progress. When the Page Program is complete, the Write Status Bit(I/O 0) may be checked(Figure 11). The internal write verify detects only errors for "1"s that are not successfully programmed to "0"s. The command register remains in Read Status command mode until another valid command is written to the command register.

Figure11. Program Operation

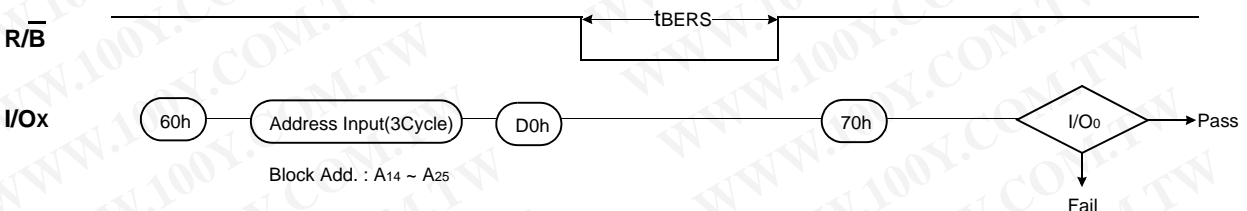


### BLOCK ERASE

The Erase operation is done on a block(16K Bytes) basis. Block address loading is accomplished in three cycles initiated by an Erase Setup command(60h). Only address A14 to A26 is valid while A9 to A13 is ignored. The Erase Confirm command(D0h) following the block address loading initiates the internal erasing process. This two-step sequence of setup followed by execution command ensures that memory contents are not accidentally erased due to external noise conditions.

At the rising edge of WE after the erase confirm command input, the internal write controller handles erase and erase-verify. When the erase operation is completed, the Write Status Bit(I/O 0) may be checked. Figure 8 details the sequence.

Figure 12. Block Erase Operation



## BLOCK PROTECT

Each block is protected from programming and erasing, controlled by the protect flag written in a specified area in the block. Block Protect operation is initiated by writing 4xh-80h-10h to the command register along with four address cycles. Only address A<sub>14</sub> to A<sub>26</sub> is valid while A<sub>0</sub> to A<sub>13</sub> is fixed as 00h. The data must not be loaded. Once the Block Protect operation starts, the Read Status Register command may be entered, with RE and CE low, to read the status register. The system controller can detect the completion of Page Program operation for protecting a block by monitoring the R/B output, or the Status bit(I/O 6) of the Status Register. Only the Read Status command and Reset command are valid while Block Protect operation is in progress. But, if Reset command is inputted while Block Protect operation is in progress, the block will not be guaranteed whether it is protected or not. When the Page Program operation for protecting a block is completed, the Write Status Bit(I/O 0) may be checked(Figure 13). The command register remains in Read Status command mode until another valid command is written to the command register.

When programming is prohibited by 41h command, the protect flag and the data of protected block can be erased by Block Erase operation. Once erasing is prohibited by 42h/43h command, the protect flag and the data of protected block can not be erased. If 80h-10h is written to command register along with four address cycles at the program protected block or at the program/erase protected block, and if 60h-D0h is written to command register along with three address cycles at the program/erase protected block, the R/B pin changes to low for t<sub>RP</sub>. The Block Protect operation must not be executed on the already protected block. The Block Protect operation will be aborted by Reset command(FFh). The Block Protect operation can only be used from first block to 200th block.

The device contains a Status Register which may be used to read out the state of the selected block. After writing 7Ah command to the command register, a read cycle outputs the content of the Status Register to the I/O pins on the falling edge of CE or RE, whichever occurs last(Figure 14). Refer to table 3 for specific Status Register definitions. The command register remains in Status Read mode until further commands are issued to it.

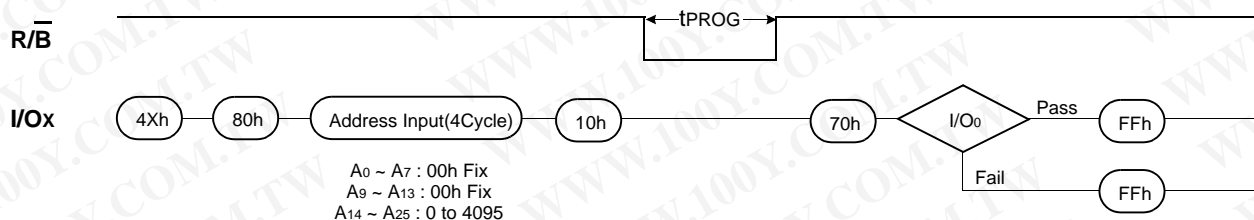
Three commands are provided to protect the block.

41h : Programming is prohibited

42h : Erasing is prohibited

43h : Both programming and erasing are prohibited

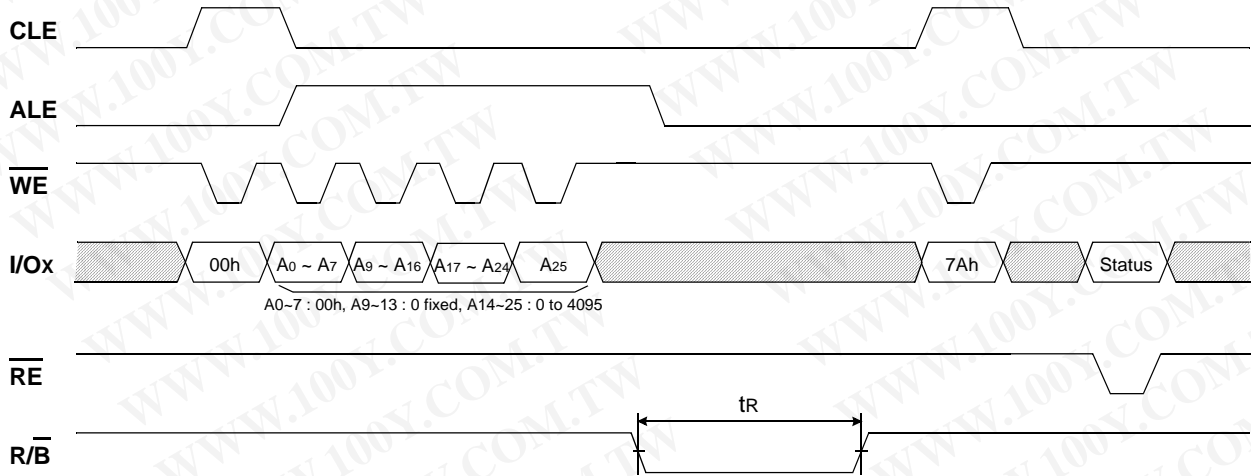
Figure 13. Block Protect Operation



**K9F1208U0C**  
**K9F1208R0C K9F1208B0C**

**FLASH MEMORY**

**Figure 14. Read Block Status**



**Table 3. Status Register Definition for 7Ah Command**

| I/O   | Status              | Definition                               |
|-------|---------------------|--|
| I/O 0 | Programming Protect | Not protected : "0"      Protected : "1" |
| I/O 1 | Erasing Protect     | Not protected : "0"      Protected : "1" |
| I/O 2 | Not use             | Don't -cared                             |
| I/O 3 | Not Use             | Don't -cared                             |
| I/O 4 | Not Use             | Don't -cared                             |
| I/O 5 | Not Use             | Don't -cared                             |
| I/O 6 | Device Operation    | Busy: "0"      Ready : "1"               |
| I/O 7 | Write Protect       | Protected : "0"      Not protect : "1"   |

**NOTE :**

1. I/Os defined 'Not use' are recommended to be masked out when Read Status is being executed.



# K9F1208U0C K9F1208R0C K9F1208B0C

## FLASH MEMORY

### READ STATUS

The device contains a Status Register which may be read to find out whether program or erase operation is completed, and whether the program or erase operation is completed successfully. After writing 70h command to the command register, a read cycle outputs the content of the Status Register to the I/O pins on the falling edge of CE or RE, whichever occurs last. This two line control allows the system to poll the progress of each device in multiple memory connections even when R/B pins are common-wired. RE or CE does not need to be toggled for updated status. Refer to table 4 for specific Status Register definitions. The command register remains in Status Read mode until further commands are issued to it. Therefore, if the status register is read during a random read cycle, a read command(00h or 50h) should be given before sequential page read cycle.

**Table 4. Status Register Definition for 70h Command**

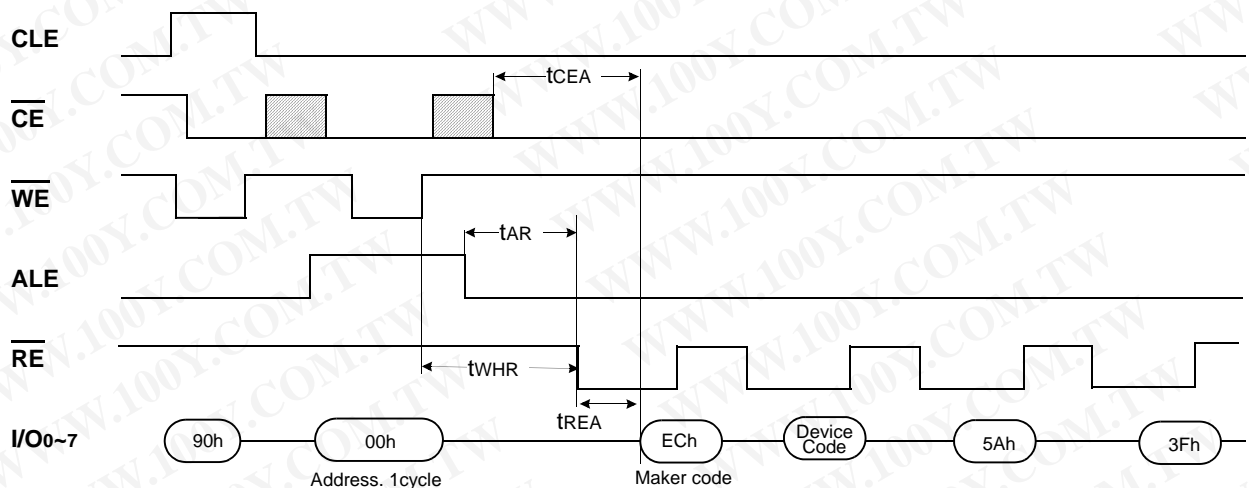
| I/O   | Page Program  | Block Erase   | Read          | Definition                          |
|-------|---------------|---------------|---------------|-------------------------------------|
| I/O 0 | Pass/Fail     | Pass/Fail     | Not use       | Pass : "0" Fail : "1"               |
| I/O 1 | Not use       | Not use       | Not use       | Don't -cared                        |
| I/O 2 | Not use       | Not use       | Not use       | Don't -cared                        |
| I/O 3 | Not Use       | Not Use       | Not Use       | Don't -cared                        |
| I/O 4 | Not Use       | Not Use       | Not Use       | Don't -cared                        |
| I/O 5 | Not Use       | Not Use       | Not Use       | Don't -cared                        |
| I/O 6 | Ready/Busy    | Ready/Busy    | Ready/Busy    | Busy : "0" Ready : "1"              |
| I/O 7 | Write Protect | Write Protect | Write Protect | Protected : "0" Not Protected : "1" |

**NOTE :** 1. I/Os defined 'Not use' are recommended to be masked out when Read Status is being executed.

### Read ID

The device contains a product identification mode, initiated by writing 90h to the command register, followed by an address input of 00h. Five read cycles sequentially output the manufacturer code(ECh), and the device code and 3rd, 4th cycle ID respectively. The command register remains in Read ID mode until further commands are issued to it. Figure 15 shows the operation sequence.

**Figure 15. Read ID Operation**



| Device     | Device Code |
|------------|-------------|
| K9F1208R0C | 36h         |
| K9F1208B0C | 76h         |
| K9F1208U0C | 76h         |

RESET

The device offers a reset feature, executed by writing FFh to the command register. When the device is in Busy state during random read, program or erase mode, the reset operation will abort these operations. The contents of memory cells being altered are no longer valid, as the data will be partially programmed or erased. The command register is cleared to wait for the next command, and the Status Register is cleared to value C0h when WP is high. If the device is already in reset state a new reset command will be accepted by the command register. The R/B pin changes to low for tRST after the Reset command is written. Refer to Figure 16 below.

Figure 16. RESET Operation

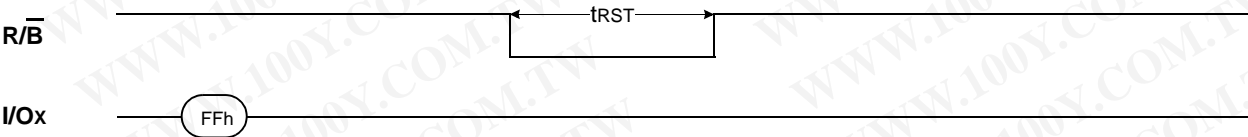


Table 5. Device Status

|                | After Power-up         | After Reset              |
|----------------|------------------------|--------------------------|
| Operation mode | 00h Command is latched | Waiting for next command |

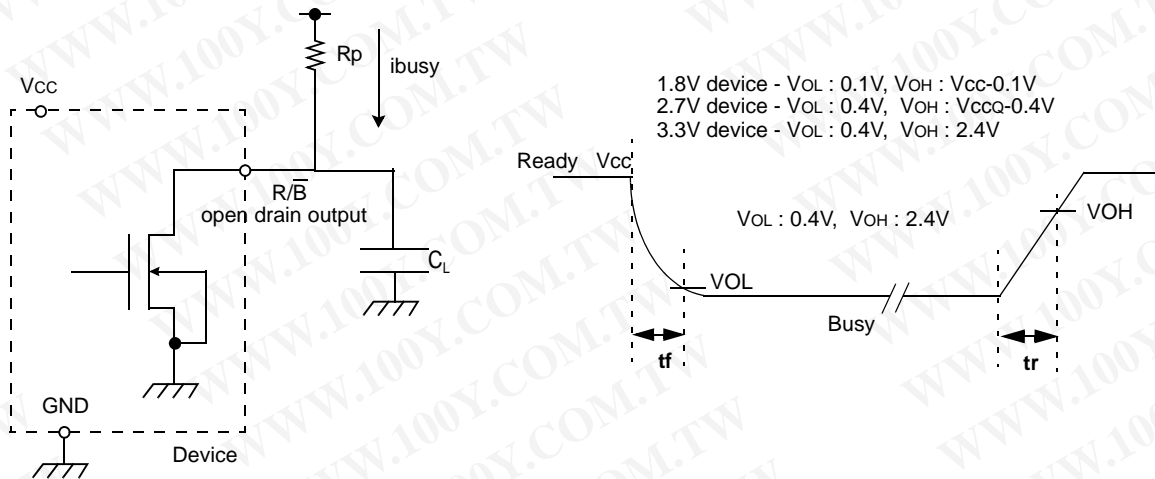
# K9F1208U0C K9F1208R0C K9F1208B0C

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勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
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## FLASH MEMORY

### READY/BUSY

The device has a  $\overline{R/B}$  output that provides a hardware method of indicating the completion of a page program, erase and random read completion. The  $\overline{R/B}$  pin is normally high but transitions to low after program or erase command is written to the command register or random read is started after address loading. It returns to high when the internal controller has finished the operation. The pin is an open-drain driver thereby allowing two or more  $\overline{R/B}$  outputs to be Or-tied. Because pull-up resistor value is related to  $t_r(\overline{R/B})$  and current drain during busy( $i_{busy}$ ), an appropriate value can be obtained with the following reference chart(Fig 17). Its value can be determined by the following guidance.

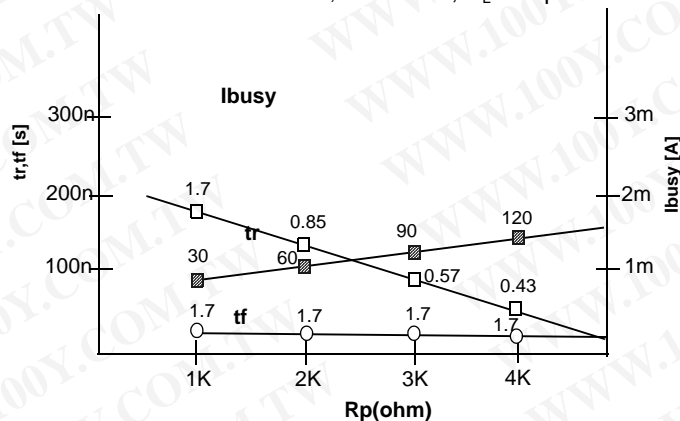


# K9F1208U0C K9F1208R0C K9F1208B0C

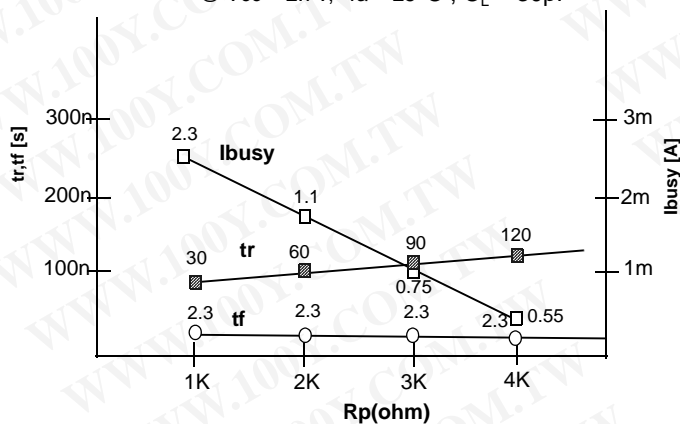
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## FLASH MEMORY

@ Vcc = 1.8V, Ta = 25°C, CL = 30pF



@ Vcc = 2.7V, Ta = 25°C, CL = 30pF



@ Vcc = 3.3V, Ta = 25°C, CL = 100pF

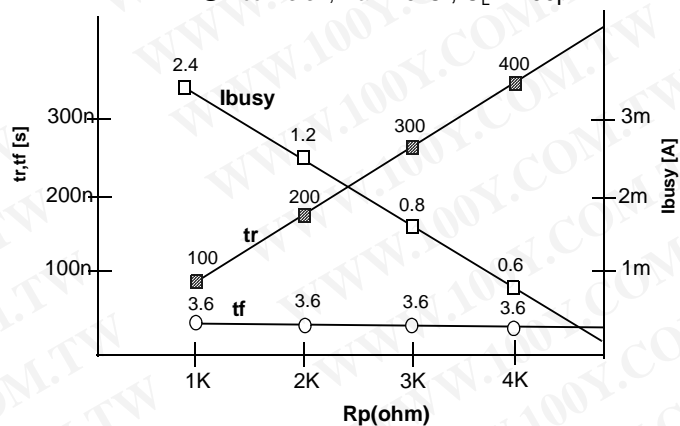


Figure 17. Rp vs tr, tf & Rp vs Ibusy

### Rp value guidance

$$Rp(\min, 1.8V \text{ part}) = \frac{V_{CC}(\text{Max.}) - V_{OL}(\text{Max.})}{I_{OL} + \sum I_L} = \frac{1.85V}{3mA + \sum I_L}$$

$$Rp(\min, 2.7V \text{ part}) = \frac{V_{CC}(\text{Max.}) - V_{OL}(\text{Max.})}{I_{OL} + \sum I_L} = \frac{2.5V}{3mA + \sum I_L}$$

$$Rp(\min, 3.3V \text{ part}) = \frac{V_{CC}(\text{Max.}) - V_{OL}(\text{Max.})}{I_{OL} + \sum I_L} = \frac{3.2V}{8mA + \sum I_L}$$

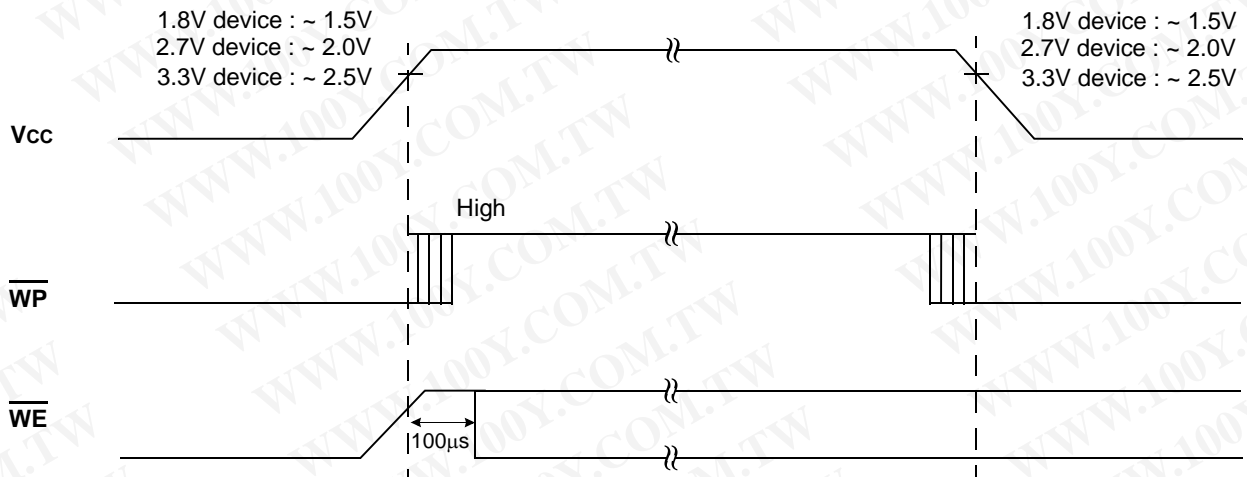
where IL is the sum of the input currents of all devices tied to the R/B pin.  
Rp(max) is determined by maximum permissible limit of tr



#### Data Protection & Power-up sequence

The device is designed to offer protection from any involuntary program/erase during power-transitions. An internal voltage detector disables all functions whenever  $V_{CC}$  is below about 1.1V(1.8V device), 1.8V(2.7V device), 2V(3.3V device).  $\overline{WP}$  pin provides hardware protection and is recommended to be kept at  $V_{IL}$  during power-up and power-down. A recovery time of minimum 100 $\mu$ s is required before internal circuit gets ready for any command sequences as shown in Figure 18. The two step command sequence for program/erase provides additional software protection.

Figure 18. AC Waveforms for Power Transition

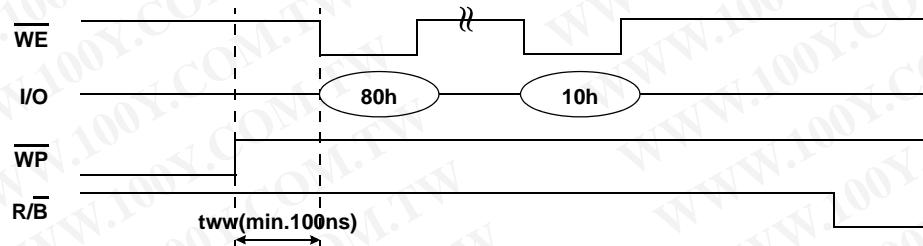


## WP AC Timing guide

Enabling WP during erase and program busy is prohibited. The erase and program operations are enabled and disabled as follows:

Figure A-1. Program Operation

### 1. Enable Mode



### 2. Disable Mode

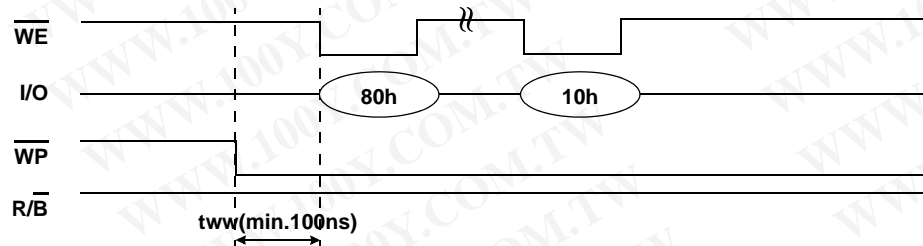
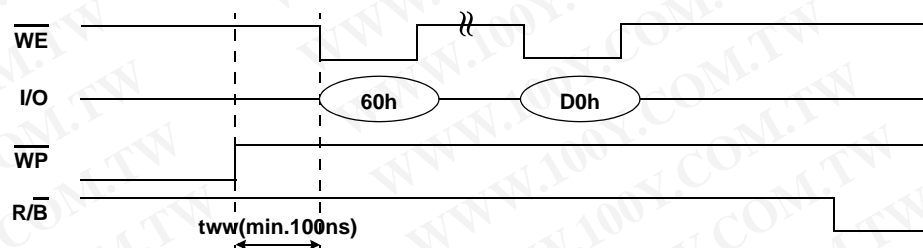


Figure A-2. Erase Operation

### 1. Enable Mode



### 2. Disable Mode

